## InnoSwitch3-Pro Family



Digitally Controllable Off-Line CV/CC QR Flyback Switcher IC with Integrated High-Voltage MOSFET, Synchronous Rectification and FluxLink Feedback

## **Product Highlights**

## Digitally Controlled via I2C Interface

- Dynamic adjustment of power supply voltage and current
- · Telemetry for power supply status and fault monitoring
- Comprehensive set of configurable protection features

#### **Highly Integrated, Compact Footprint**

- Multi-mode Quasi-Resonant (QR) / DCM / CCM flyback controller, 650 V or 725 V MOSFET, secondary-side sensing and synchronous rectifier driver
- · Optimized efficiency across line and load range
- Integrated FluxLink<sup>™</sup>, HIPOT-isolated, feedback link
- Instantaneous transient response
- · Drives low-cost N-channel MOSFET series load switch
- Integrated 3.6 V supply for external MCU

## **EcoSmart™ - Energy Efficient**

- Less than 30 mW no-load including line sense and MCU
- Enables power supply designs that easily comply with all global energy efficiency regulations
- · Low heat dissipation

#### **Advanced Protection / Safety Features**

- Input voltage monitoring with accurate brown-in/brown-out and overvoltage protection
- Output OV/UV fault detection with independently configured responses
- Secondary FET / diode short protection
- Open SR FET gate detection
- · Hysteretic thermal shutdown
- · Programmable watchdog timer for system faults

#### **Full Safety and Regulatory Compliance**

- Reinforced insulation
- Isolation voltage >4000 VAC
- 100% production HIPOT compliance testing
- · UL1577 and TUV (EN60950) safety approved

## **Green Package**

· Halogen free and RoHS compliant

#### **Applications**

- High efficiency USB PD 3.0 + PPS/QC adapters
- · Multiprotocol adapters including QuickCharge, AFC, FCP, SCP
- Direct-charge mobile device chargers
- Multi-chemistry tool and general purpose battery chargers
- · Adjustable CV and CC LED ballast

#### **Description**

The InnoSwitch<sup>TM</sup>3-Pro series family of ICs dramatically simplifies the development and manufacturing of fully programmable, highly efficient power supplies, particularly those in compact enclosures. The universal  $I^2C$  interface enables dynamic control of output voltage and current along with many configurable features. Telemetry provides reporting of programmed features and fault modes.

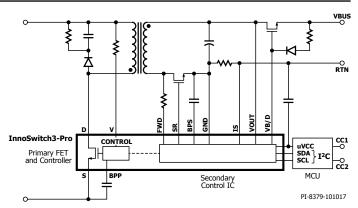


Figure 1. Typical Application.



Figure 2. High Creepage, Safety-Compliant InSOP-24D Package.

#### Output Power Table<sup>1</sup>

	230 VAC	± 15%	85-265 VAC		
Product <sup>4,5</sup>	Adapter <sup>2</sup>	Open Frame³	Adapter <sup>2</sup>	Open Frame³	
INN3365C/3375C	25 W	30 W	22 W	25 W	
INN3366C/3376C	35 W	40 W	27 W	36 W	
INN3377C	40 W	45 W	36 W	40 W	
INN3367C	45 W	50 W	40 W	45 W	
INN3368C	55 W	65 W	50 W	55 W	

Table 1. Output Power Table. Notes:

- Maximum output power is dependent on the design, with maximum IC package temperature kept <125 °C.</li>
- Minimum continuous power in a typical non-ventilated enclosed typical size adapter measured at 40 °C ambient.
- 3. Minimum peak power capability.
- 4. C Package: InSOP-24D.
- 5. INNxx6xC 650 V MOSFET, INNxx7xC 725 V MOSFET.

InnoSwitch3-Pro devices are ideal for AC/DC power supply applications where fine (10 mV, 50 mA) output voltage and current adjustment are necessary. Typical implementations comprise a system microprocessor or dedicated microcontroller with an  $\rm I^2C$  port that is used to configure, control and supervise operation of the power sub-system. The uVCC pin provides a bias supply for the microprocessor in stand-alone implementations such as USB PD adapters and chargers.

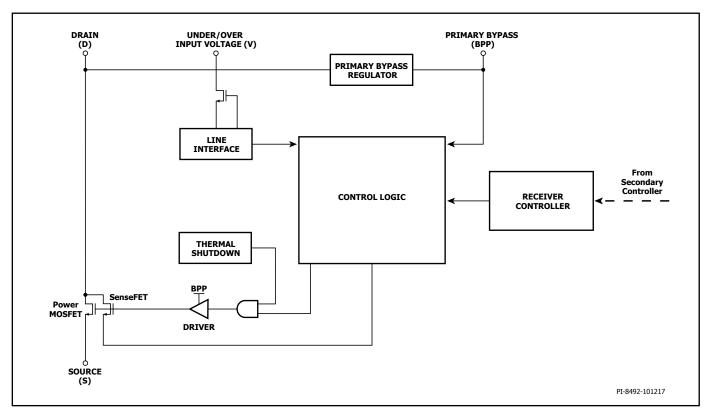


Figure 3. Primary Controller Block Diagram.

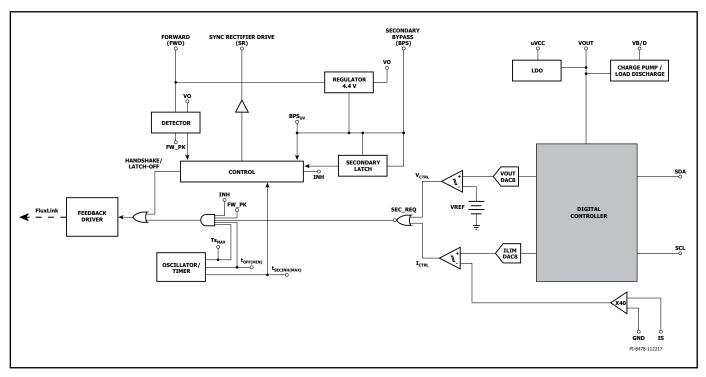


Figure 4. Secondary Controller Block Diagram.

## **Pin Functional Description**

#### ISENSE (IS) Pin (Pin 1)

Connection to the power supply return output terminals. An external current sense resistor should be connected between this and the SECONDARY GROUND pin.

#### **SECONDARY GROUND (GND) (Pin 2)**

GND for the secondary IC. Note this is not the power supply output GND due to the presence of the sense resistor between this and the ISENSE pin.

#### NC Pin (Pin 3)

Leave open. Should not be connected to any other pins.

#### SECONDARY BYPASS (BPS) Pin (Pin 4)

It is the connection point for an external bypass capacitor for the secondary IC supply.

#### I<sup>2</sup>C Clock (SCL) Pin (Pin 5)

 $\rm I^2C$  serial communication protocol clock line sourced by the Bus master (max 700 kHz).

## I<sup>2</sup>C Serial Data (SDA) Pin (Pin 6)

 $\rm I^2C$  serial communication protocol data line sourced by the Bus master (max 700 kHz).

#### External VCC Supply (uVCC) Pin (Pin 7)

This is a 3.6 V supply for an external controller.

## VBUS Series Switch Drive and Load Discharge (VB/D) Pin (Pin 8)

VBUS enable and driver for NMOS gate for VOUT to VBUS pass MOSFETs. This pin can also be used to discharge output load voltage.

## **SYNCHRONOUS RECTIFIER DRIVE (SR) Pin (Pin 9)**

Gate driver output and connection to external SR FET gate terminal.

## **OUTPUT VOLTAGE (VOUT) Pin (Pin 10)**

Connected directly to the output voltage providing current for the secondary IC and sense for output voltage regulation. Also active pull-down current source for minimum load.

## FORWARD (FWD) Pin (Pin 11)

The connection point to the switching node of the transformer output winding providing information on the primary switch timing plus providing power for the secondary IC when  $V_{\text{OUT}}$  is below a threshold value.

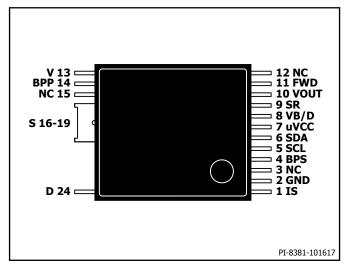


Figure 5. Pin Configuration.

#### NC Pin (Pin 12)

Leave open. Should not be connected to any other pins.

## **UNDER/OVER INPUT VOLTAGE (V) Pin (Pin 13)**

A high-voltage pin connected to the AC or DC side of the input bridge for detecting under and overvoltage conditions at the power supply input. When connected to the AC side of the bridge, a high-voltage switch is opened when not sensing to reduce power consumption. This pin should be tied to GND to disable UV/OV protection.

## PRIMARY BYPASS (BPP) Pin (Pin 14)

It is the connection point for an external bypass capacitor for the primary IC supply. This is also the ILIM selection pin for choosing standard ILIM or ILIM+1.

## NC Pin (Pin 15)

Leave open. Should not be connected to any other pins.

#### SOURCE (S) Pin (Pin 16-19)

These pins are the power MOSFET source connection. It is also ground reference for primary BYPASS pin.

## DRAIN (D) Pin (Pin 24)

This pin is the power MOSFET drain connection.

## **InnoSwitch3-Pro Functional Description**

The InnoSwitch3-Pro combines a high-voltage power MOSFET switch, along with both primary-side and secondary-side controllers in one device.

The architecture incorporates a novel inductive coupling feedback scheme using the package lead frame and bond wires to provide a safe, reliable, and low-cost means to communicate accurate direct sensing of the output voltage and output current on the secondary IC to the primary IC.

The primary controller on InnoSwitch3-Pro is a Quasi-Resonant (QR) flyback controller that has the ability to operate in continuous conduction mode (CCM). The controller uses both variable frequency and variable current control schemes. The primary controller consists of a frequency jitter oscillator; a receiver circuit magnetically coupled to the secondary controller, a current limit controller, 5 V regulator on the PRIMARY BYPASS pin, audible noise reduction engine for light load operation, bypass overvoltage detection circuit, a lossless input line sensing circuit, current limit selection circuitry, over-temperature protection, leading edge blanking, secondary output diode/SR FET short protection circuit and a 650 V / 725 V power MOSFET.

The InnoSwitch3-Pro secondary controller consists of a transmitter circuit that is magnetically coupled to the primary receiver, an  $I^2C$  interface to control power supply parameters and telemetry functions, a 4.4 V regulator on the SECONDARY BYPASS pin, synchronous rectifier MOSFET driver, QR mode circuit, oscillator and timing functions, and a host of integrated protection features.

Figure 3 and Figure 4 show the functional block diagrams of the primary and secondary controller with the most important features.

#### **Primary Controller**

InnoSwitch3-Pro has variable frequency QR controller plus CCM/CrM/DCM operation for enhanced efficiency and extended output power capability.

## **PRIMARY BYPASS Pin Regulator**

The PRIMARY BYPASS pin has an internal regulator that charges the PRIMARY BYPASS pin capacitor to  $V_{\rm BPP}$  by drawing current from the DRAIN pin whenever the power MOSFET is off. The PRIMARY BYPASS pin is the internal supply voltage node. When the power MOSFET is on, the device operates from the energy stored in the PRIMARY BYPASS pin capacitor.

In addition, a shunt regulator clamps the PRIMARY BYPASS pin voltage to  $V_{\text{SHUNT}}$  when current is provided to the PRIMARY BYPASS pin through an external resistor. This allows the InnoSwitch3-Pro to be powered externally through a bias winding, decreasing the no-load consumption to less than 30 mW in a 5 V output design.

#### **Primary Bypass ILIM Programming**

InnoSwitch3-Pro ICs allows the user to adjust current limit (ILIM) settings through the selection of the PRIMARY BYPASS pin capacitor value. A ceramic capacitor can be used.

There are 2 selectable capacitor sizes - 0.47  $\mu\text{F}$  and 4.7  $\mu\text{F}$  for setting standard and increased ILIM settings respectively.

#### **Primary Bypass Undervoltage Threshold**

The PRIMARY BYPASS pin undervoltage circuitry disables the power MOSFET when the PRIMARY BYPASS pin voltage drops below ~4.5 V ( $V_{\text{BPP}}$  -  $V_{\text{BP(H)}}$ ) in steady-state operation. Once the PRIMARY BYPASS pin voltage falls below this threshold, it must rise to  $V_{\text{BP}}$  to re-enable turn-on of the power MOSFET.

#### **Primary Bypass Output Overvoltage Function**

The PRIMARY BYPASS pin has a latching OV protection feature. A Zener diode in parallel with the resistor in series with the PRIMARY BYPASS pin capacitor is typically used to detect an overvoltage on the primary bias winding and activate the protection mechanism. In the event that the current into the PRIMARY BYPASS pin exceeds ISD, the device will latch-off or disable the power MOSFET switching for a time  $t_{\mbox{\tiny AR(OFF})'}$  after which time the controller will restart and attempt to return to regulation.

VOUT OV protection is also included as an integrated feature on the secondary controller.

#### **Over-Temperature Protection**

The thermal shutdown circuitry senses the primary MOSFET die temperature. The threshold is set to  $T_{\rm SD}$  with either a hysteretic or latch-off response.

Hysteretic response: If the die temperature rises above the threshold, the power MOSFET is disabled and remains disabled until the die temperature falls by  $T_{\text{SD(H)}}$  at which point switching is re-enabled. A large amount of hysteresis is provided to prevent over-heating of the PCB due to a continuous fault condition.

Latch-off response: If the die temperature rises above the threshold the power MOSFET is disabled. The latching condition is reset by bringing the PRIMARY BYPASS pin below  $V_{\text{BPP(RESET)}}$  or by going below the UNDER/OVER INPUT VOLTAGE pin UV  $(I_{\text{UV}})$  threshold.

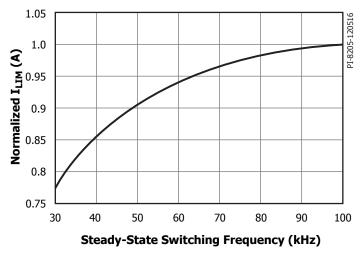


Figure 6. Normalized Primary Current vs. Frequency.

#### **Current Limit Operation**

The primary-side controller has a current limit threshold ramp that is inversely proportional to the time from the end of the previous primary switching cycle (i.e. from the time the primary MOSFET turns off at the end of a switching cycle).

This characteristic produces a primary current limit that increases as the switching frequency (load) increases (Figure 6).

This algorithm enables the most efficient use of the primary switch with the benefit that this algorithm responds to digital feedback information immediately when a feedback switching cycle request is received.

At high load, switching cycles have a maximum current approaching 100%  $I_{\text{LIM}}$ . This gradually reduces to 30% of the full current limit as load decreases. Once 30% current limit is reached, there is no further reduction in current limit (since this is low enough to avoid audible noise). The time between switching cycles will continue to increase as load reduces.

#### **Jitter**

The normalized current limit is modulated between 100% and 95% at a modulation frequency of  $f_M$  this results in a frequency jitter of  $\sim$ 7 kHz with average frequency of  $\sim$ 100 kHz.

#### **Auto-Restart**

In the event a fault condition occurs (such as an output overload, output short-circuit, or external component/pin fault), the InnoSwitch3-Pro enters auto-restart (AR) or latches off. The latching condition is reset by bringing the PRIMARY BYPASS pin below  $\sim 3~\rm V$  or by going below the UNDER/OVER INPUT VOLTAGE pin UV ( $\rm I_{UV}$ ) threshold.

In auto-restart, switching of the power MOSFET is disabled for  $t_{\text{AR(OFF)}}$ . There are 2 ways to enter auto-restart:

- 1. Continuous secondary requests at above the overload detection frequency ( $\sim$ 110 kHz) for longer than 82 ms ( $t_{_{AR}}$ ).
- 2. No requests for switching cycles from the secondary for  $> t_{AR/SK}$ .

The second is included to ensure that if communication is lost, the primary tries to restart. Although this should never be the case in normal operation, it can be useful when system ESD events (for example) causes a loss of communication due to noise disturbing the secondary controller. The issue is resolved when the primary restarts after an auto-restart off-time.

The first auto-restart off-time is short ( $t_{AR(OFF)SH}$ ). This short auto-restart time is to provide quick recovery under fast reset conditions. The short auto-restart off-time allows the controller to quickly check to determine whether the auto-restart condition is maintained beyond  $t_{AR(OFF)SH}$ .

The auto-restart is reset as soon as an AC reset occurs.

#### **SOA Protection**

In the event that there are two consecutive cycles where the  $I_{\text{LIM}}$  is reached within  ${\sim}500$  ns (the blanking time + current limit delay time), the controller will skip 2.5 cycles or  ${\sim}25~\mu s$  (based on full frequency of 100 kHz). This provides sufficient time for the transformer to reset with large capacitive loads without extending the start-up time.

#### **Input Line Voltage Monitoring**

The UNDER/OVER INPUT VOLTAGE pin is used for input undervoltage and overvoltage sensing and protection.

A 4 M $\Omega$  resistor is tied between the high-voltage DC bulk capacitor after the bridge (or to the AC side of the bridge rectifier for fast AC reset) and the UNDER/OVER INPUT VOLTAGE pin to enable this functionality. This function can be disabled by shorting the UNDER/OVER INPUT VOLTAGE pin to primary GND.

At power-up, after the primary bypass capacitor is charged and the ILIM state is latched, and prior to switching, the state of the UNDER/OVER INPUT VOLTAGE pin is checked to confirm that it is above the brown-in and below the overvoltage shutdown thresholds.

In normal operation, if the UNDER/OVER INPUT VOLTAGE pin current falls below the brown-out threshold and remains below brown-in for longer than  $t_{\text{UV}}$ , the controller enters auto-restart. Switching will only resume once the UNDER/OVER INPUT VOLTAGE pin current is above the brown-in threshold.

In the event that the UNDER/OVER INPUT VOLTAGE pin current is above the overvoltage threshold, the controller will also enter auto-restart. Again, switching will only resume once the UNDER/OVER INPUT VOLTAGE pin current has returned to within its normal operating range.

The input line UV/OV function makes use of a internal high-voltage ( $V_{\nu}$ ) MOSFET on the UNDER/OVER INPUT VOLTAGE pin to reduce power consumption. The controller samples the input line at light load conditions when the time between switching cycles is 50 µsec or more. At >50 µsec between switching cycles, the high-voltage MOSFET will remain on making sensing continuous.

## **Primary-Secondary Handshake**

At start-up, the primary-side initially switches without any feedback information (this is very similar to the operation of a standard TOPSwitch™, TinySwitch™ or LinkSwitch™ controllers).

If no feedback signals are received during the auto-restart on-time  $(t_{_{AR}})$ , the primary goes into auto-restart mode. Under normal conditions, the secondary controller will power-up via the FORWARD pin or from the OUTPUT VOLTAGE pin and take over control. From this point onwards the secondary controls switching.

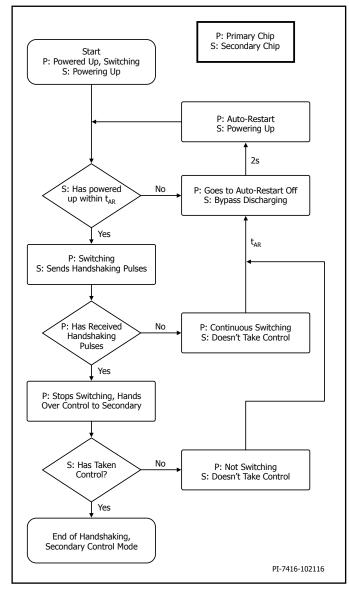


Figure 7. Primary-Secondary Handshake Flow Chart.

If the primary controller stops switching or does not respond to cycle requests from the secondary during normal operation (when the secondary has control), the handshake protocol is initiated to ensure that the secondary is ready to assume control once the primary begins to switch again. An additional handshake is also triggered if the secondary detects that the primary is providing more cycles than were requested.

The most likely event that could require an additional handshake is when the primary stops switching as the result of a momentary line brown-out event. When the primary resumes operation, it will default to a start-up condition and attempt to detect handshake pulses from the secondary.

If secondary does not detect that the primary responds to switching requests for 6 consecutive cycles, or if the secondary detects that the primary is switching without cycle requests for 6 or more consecutive cycles, the secondary controller will initiate a second handshake sequence. This provides additional protection against cross-conduction of the SR FET while the primary is switching. This protection mode also prevents an output overvoltage condition in the event that the primary is reset while the secondary is still in control.

#### **Wait and Listen**

When the primary resumes switching after initial power-up recovery from an input line voltage fault (UV or OV) or an auto-restart event, it will assume control and require a successful handshake to relinquish control to the secondary controller.

As an additional safety measure the primary will pause for an auto-restart on-time period,  $t_{_{AR}}$  (~82 ms), before switching. During this "wait" time, the primary will "listen" for secondary requests. If it sees two consecutive secondary requests, separated by ~30 ms, the primary will infer secondary control and begin switching in slave mode. If no pulses occur during the  $t_{_{AR}}$  "wait" period, the primary will begin switching under primary control until handshake pulses are received

#### **Audible Noise Reduction Engine**

The InnoSwitch3-Pro features an active audible noise reduction mode whereby the controller (via a "frequency skipping" mode of operation) avoids the resonant band (where the mechanical structure of the power supply is most likely to resonate – increasing noise amplitude) between 7 kHz and 12 kHz - 142  $\mu s$  and 83  $\mu s$ . If a secondary controller switch request occurs within this time window from the last conduction cycle, the gate drive to the power MOSFET is inhibited.

#### **Secondary Controller**

As shown in the block diagram in Figure 4, the IC is powered through regulator 4.4 V block by either VOUT or FW connections to the SECONDARY BYPASS pin. The SECONDARY BYPASS pin is connected to an external decoupling capacitor and fed internally from the regulator block.

The FORWARD pin also connects to the negative edge detection block used for both handshaking and timing to turn on the SR FET connected to the SYNCHRONOUS RECTIFIER DRIVE pin. The FORWARD pin is used to sense when to turn off the SR FET in discontinuous mode operation when the voltage across the FET on resistance drops below the  $V_{\text{SR(TH)}}$  threshold.

In continuous conduction mode (CCM) operation of the SR FET is turned off when the feedback pulse is sent to demand the next switching cycle, providing excellent synchronous operation, free of any overlap for the FET turn-off while operating in continuous mode.

The output voltage is regulated on the VOUT pin and defaults to 5 V at start-up.

The external current sense resistor connected between ISENSE and SECONDARY GROUND pins regulates the output current in constant current regulator mode.

#### **Programmable Voltage and Current**

The operating voltage and current set points are set fully programmable through I2C interface. The output voltage is fully user programmable with a range from 3 V to 24 V. The fast response feedback loop of the IC features 10 mV ( $\Delta V_{\text{OUT}}$ ) voltage change resolution. The programmable current set point features 20% to 100% operating range, with a programming step size of 0.8% of full scale current. Below 5 V and for load current less than 50 mA, voltage command step size of 10 mV may result in non-montonicity since operating frequency is very low.

#### Internal uVCC Generation, Bus Switch Driver and Discharge

The internal LDO generates 3.6 V uVCC for MCU which simplifies the system design. InnoSwitch3-Pro also has an internal driver that guarantees turn-on of an n-channel MOSFET series bus switch with source voltage as high as 24 V. The VB/D pin which enables the bus switch is also configurable as the discharge path for the load.

#### **Programmable Protections**

User programmable protection features include output undervoltage (UV) and overvoltage (OV) protection and over-temperature protection. The UV/OV thresholds are dynamically programmable. Users can program three responses to these protections, including auto-restart, latch-off and no-response. An auto-restart (AR) or latch-off (LO) response does not inherently open the series bus switch. The I<sup>2</sup>C master must send a command to open it if this is the desired behavior.

The secondary controller also features generation of an interrupt signal if one or more of the faults is detected. The SCL pin is pulled down for  $\sim$ 55  $\mu$ s to generate an interrupt for MCU.

In the case when the MCU loses communication with the secondary controller, a watchdog timer triggers a reset to reassert a safe 5 V condition and opens the series bus switch.

#### **Telemetry Feature**

The controller communicates to the MCU to report back the status of the power supply. Output voltage and current is measured by internal ADC and available to MCU through I<sup>2</sup>C. The telemetry features also covers CV, CC and constant power set points, OV/UV thresholds, all protection settings, interrupt status, and complete fault status.

#### **Minimum Off-Time**

The secondary controller initiates a cycle request using the inductiveconnection to the primary. The maximum frequency of secondarycycle requests is limited by a minimum cycle off-time of  $t_{\mbox{\scriptsize OFF(MIN)}}.$  This is in order to ensure that there is sufficient reset time after primary conduction to deliver energy to the load.

#### **Maximum Switching Frequency**

The maximum switch-request frequency of the secondary controller is f<sub>sreo</sub>.

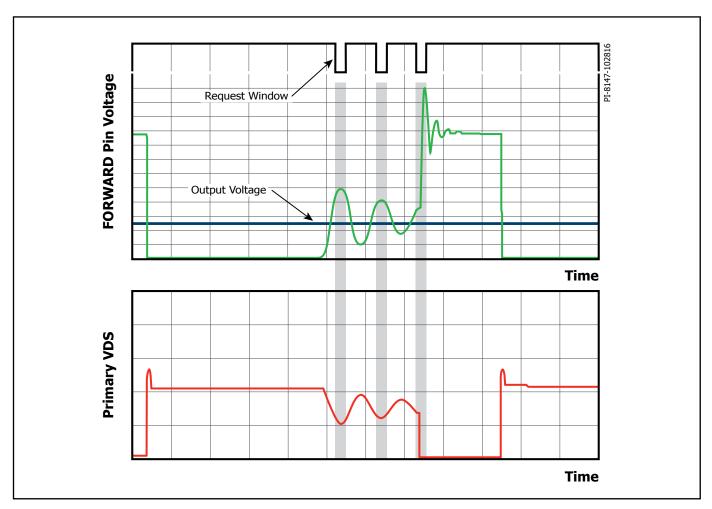


Figure 8. Intelligent Quasi-Resonant Mode Switching.

## InnoSwitch3-Pro

#### **Frequency Soft-Start**

At start-up the primary controller is limited to a maximum switching frequency of  $f_{\text{SW}}$  and 70% of the maximum programmed current limit (at  $f_{\text{SRFO}}$  operation).

After hand-shake is completed the secondary controller linearly ramps up the switching frequency from  $f_{\text{SW}}$  to  $f_{\text{SREQ}}$  over the  $t_{\text{SS(RAMP)}}$  time period.

In the event of a short-circuit or overload at start-up, the device will move directly into CC (constant-current) mode. The device will go into auto-restart (AR), if the output voltage does not rise above the 3.6 V before the expiration of the soft start timer  $(t_{\text{SS(RAMP)}})$  after handshake has occurred.

If the output voltage reaches regulation within the  $t_{\rm SS(RAMP)}$  time period, the frequency ramp is immediately aborted and the secondary controller is permitted to go full frequency. This will allow the controller to maintain regulation in the event of a sudden transient loading soon after regulation is achieved. The frequency ramp will only be aborted if quasi-resonant-detection programming has already occurred.

### **Maximum Secondary Inhibit Period**

Secondary requests to initiate primary switching are inhibited to maintain operation below maximum frequency and ensure minimum off-time. Besides these constraints, secondary-cycle requests are also inhibited during the "ON" time cycle of the primary switch (time between the cycle request and detection of FORWARD pin falling edge). The maximum time-out in the event that a FORWARD pin falling edge is not detected after a cycle requested is  $\sim 30~\mu s$ .

#### **Output Voltage Weak Bleeder**

In the event that the sensed voltage on the OUTPUT VOLTAGE pin is 2% higher than the regulation threshold, a bleed current of  $\sim\!\!2.5$  mA (3 mA max) is applied on the OUTPUT VOLTAGE pin (weak bleed). The current sink on the OUTPUT VOLTAGE pin is intended to discharge the output voltage after momentary overshoot events. The secondary does not relinquish control to the primary during this mode of operation.

#### **SECONDARY BYPASS Pin Overvoltage Protection**

The InnoSwitch3-Pro secondary controller features a SECONDARY BYPASS pin OV feature similar to PRIMARY BYPASS pin OV feature. When the secondary is in control, in the event that the SECONDARY BYPASS pin current exceeds  $\mathbf{I}_{\text{BPS(SD)}}$  the secondary will send a command to the primary to initiate an auto-restart off-time ( $\mathbf{t}_{\text{AR(OFF)}}$ ) or latch-off.

#### **SR Disable Protection**

In each cycle SR is only engaged if a set cycle was requested by the secondary controller and the negative edge is detected on the FORWARD pin. In the event that the voltage on the ISENSE pin exceeds approximately 3 times the CC threshold, the SR FET drive is disabled until the surge current has diminished to nominal levels.

#### **SR Static Pull-Down**

To ensure that the SR gate is held low when the secondary is not in control, the SYNCHRONOUS RECTIFIER DRIVE pin has a nominally "ON" device to pull the pin low and reduce any voltage on the SR gate due to capacitive coupling from the FORWARD pin.

#### **Open SR Protection**

In order to protect against an open SYNCHRONOUS RECTIFIER DRIVE pin system fault the secondary controller has a protection mode to ensure the SYNCHRONOUS RECTIFIER DRIVE pin is connected to an external FET. At start-up the controller will apply a current to the SYNCHRONOUS RECTIFIER DRIVE pin; an internal threshold will correlate to a capacitance of 100 pF. If the external capacitance on the SYNCHRONOUS RECTIFIER DRIVE pin is below 100 pF the resulting voltage is above the reference voltage, and the device will assume the SYNCHRONOUS RECTIFIER DRIVE pin is "open" and there is no FET to drive. If the pin capacitance detected is above 100 pF (the resulting voltage is below the reference voltage), the controller will assume an SR FET is connected.

In the event the SYNCHRONOUS RECTIFIER DRIVE pin is detected to be open, the secondary controller will stop requesting pulses from the primary to initiate auto-restart.

If the SYNCHRONOUS RECTIFIER DRIVE pin is tied to ground at start-up, the SR drive function is disabled and the open SYNCHRONOUS RECTIFIER DRIVE pin protection mode is also disabled.

#### **Intelligent Quasi-Resonant Mode Switching**

In order to improve conversion efficiency and reduce switching losses, the InnoSwitch3-Pro features a means to force switching when the voltage across the primary switch is near its minimum voltage when the converter operates in discontinuous conduction mode (DCM). This mode of operation is automatically engaged in DCM and disabled once the converter moves to continuous-conduction mode (CCM). See Figure 8.

Rather than detecting the magnetizing ring valley on the primaryside, the peak voltage of the FORWARD pin voltage as it rises above the output voltage level is used to gate secondary requests to initiate the switch "ON" cycle in the primary controller.

The secondary controller detects when the controller enters in discontinuous-mode and opens secondary cycle request windows corresponding to minimum switching voltage across the primary power MOSFET.

Quasi-Resonant (QR) mode is enabled for 20  $\mu$ sec after DCM is detected. QR switching is disabled after 20  $\mu$ sec, at which point switching may occur at any time a secondary request is initiated.

The secondary controller includes blanking of  $\sim\!\!1~\mu s$  to prevent false detection of primary "ON" cycle when the FORWARD pin rings below ground.

## **Register Definition**

#### I<sup>2</sup>C Slave Address

The InnoSwitch3-Pro 7-bit slave address is 0x18 (7'b001 1000).

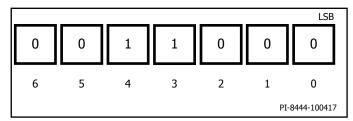


Figure 9. PI Slave Address.

## I<sup>2</sup>C Protocol Format is 3-Byte Write Command

Write commands:

[PI\_SLAVE\_ADDRESS][W][A][PI\_COMMAND][A][Byte][A] or [PI\_SLAVE\_ADDRESS][W][A][PI\_COMMAND][A][Low Byte][A][High Byte][A]

#### Write and Read Command I<sup>2</sup>C Protocol

[A] denotes a Slave Acknowledgement

[a] denotes a Master Acknowledgement

[na] denotes a Master nack

[W] denotes Write (1'b0)

[r] denotes Read (1'b1)

 $[PI\_SLAVE\_ADDRESS] = 0x18 (7'b001 1000)$ 

[PI\_COMMAND] (see PI COMMAND Register Address Assignments,

Description and Control Range Section)

[TELEMETRY\_REGISTER\_ADDRESS] (see Telemetry (Read-Back) Registers Address Assignment and Description Section)

Every I<sup>2</sup>C transaction should have at least a 150 μsec delay between commands. If this delay is not provided commands may be ignored.

The InnoSwitch3-Pro does not support clock stretching.

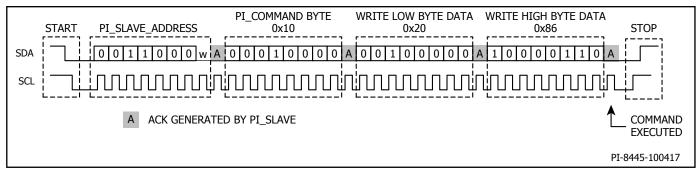


Figure 10. Example Register Write Command Sequence (CV set to 8 V).

#### I<sup>2</sup>C Protocol Format is 2-Byte Read Command

Word Read transaction:

[PI\_SLAVE\_ADDRESS][W][A][PI\_COMMAND][A][START\_TELEMETRY\_REGISTER\_ADDRESS]

[A][END\_TELEMETRY\_REGISTER\_ADDRESS [A]

[PI\_SLAVE\_ADDRESS] [r][A]{PI Slave responds Low Byte}[a]{PI Slave

responds High Byte}[na] READ REGISTER **START** PI SLAVE ADDRESS 0x80

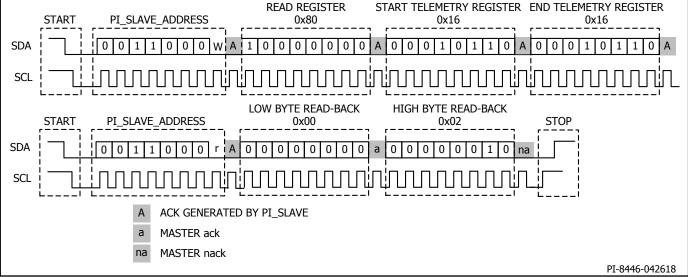


Figure 11. Example Read Register Sequence (Read Fault Register READ11). Note: START and END TELEMETRY Register Addresses Does Not Have to Point to Same Register to Read multiple Registers in Single Command.

## PI COMMAND Register Address Assignments, Description and Control Range

All command register addresses in InnoSwitch3-Pro are odd-parity addressing. Some select registers (some highlighted below) also employ odd parity error bit to the high and low bytes of data.

			Registe	r Address																
Name	Function	Adjustment Range	Address	Address with Odd Parity	Туре	Type Default		Description												
				1			bit[7]	Parity												
VBEN	Series Bus Switch Control	Enable or Disabled?	0x	<b>c</b> 04	WR_Byte	0x0	bit[1:0]	{11} Enable VBEN {00} Disable VBE												
BLEEDER	Activate Bleeder (V <sub>оит</sub> ) Function	Enable or Disabled?	0x06	0x86	WR_Byte	0x0	bit[0]	{0}: Disabled {1}: Enabled OTP clears this re	egister											
							bit[7]	Parity												
VDIS	Load (VBUS) Discharge	Enable or Disabled?	0x	08	W/R_Byte	0x0	bit[1:0]	{11} Enable Discl VBEN	narge/Disable											
				1			bit[3:2]	{11} Disable Disc	harge											
Turn-Off PSU	Latch-off Device	Enable or Disabled?	0x0A	0x8A	W/R_Byte	0x0	bit[0]	{0}: Disabled {1}: Enabled												
Fast VI Command	Speed of CV/CC Update	10 ms Update Limit or No Speed Limit?	0x0C	0x8C	W/R_Byte	0x0	bit[0]	{1}: Disable 10 n limit	nsec update											
CVO	Constant- Voltage Only	Only CV Mode	0x	(0E	W/R_Byte	0x0	bit[0]	{1}: CV Only Mode/No CC Regulation												
							bit[15]	High Byte Parity												
CV	Output Voltage	3 V to 24 V (10 mV/step)	0x	0x10	W/R_Word	W/R_Word	500 (5 V)	bit[12:8]		Range {300 to 2400}										
							bit[7]	Low Byte Parity	10 mV/LSB											
							bit[6:0]													
							bit[15]	High Byte Parity	-											
OVA	Overvoltage Threshold	6.2 V to 25 V (100 mV/step)	0x12	0x12	0x12	0x12	0x12	0x12	0x12	0x12	0x12	0x12	0x12	0x12	0x92	W/R_Word	62 (6.2 V)	bit[8]		Range {62 to 250}
							bit[7]	Low Byte Parity	100 mV/LSB											
							bit[6:0]													
							bit[15]	High Byte Parity	-											
UVA	Undervoltage Threshold	3 V to 24 V (100 mV/step)	0x14	0x94	W/R_Word	36 (3.6 V)	bit[8]		Range {30 to 240} 100 mV/LSB											
		,,,,,,					bit[7]	Low Byte Parity												
							bit[6:0]													
CDC	Cable Drop Compensation	0 mV to 600 mV (50 mV/step)	0x	(16	W/R_Word	0 (0 V)	bit[3:0]	Range {0 to 12} 50 mV/LSB												
							bit[15]	High Byte Parity												
CC	Constant Current		0x18	0x98	0x98	0x98	0x98	0x98	0x98	W/R_Word	128 (100%)	bit[8]		Range {25 (20%) to 128						
	Regulation	step/Rs)				(10070)	bit[7]	Low Byte Parity	(100%)}											
										bit[6:0]										

Table 2. Command Register Assignments.

			Register Address						
Name	Function	Adjustment Range	Address	Address with Odd Parity	Туре	Default		Description	
							bit[15]	High Byte Parity	
$V_{_{\mathrm{KP}}}$	Constant Output Power	5.3 V to 24 V (100 mV/step)	0x	1A	W/R_Word	240 (24V)	bit[8]	Range {53 to 240} 100 mV/LSB	
	Knee Voltage						bit[7]	Low Byte Parity	
							bit[6:0]		
OVL	Overvoltage Fault Response	Latch-off or AR or No Response?	0x	:1C	W/R_Byte	0x02	bit[1:0]	{00}: No Response {01}: Latch-off {10}: Auto-Restart	
UVL	Undervoltage Fault Response	Latch-off or AR or No Response?	0x1E	0x9E	W/R_Byte	0x0	bit[1:0]	{00}: Auto-Restart {01}: Latch-off {10}: No Response	
	IS-pin Short	Latch-off or AR or No Response?					bit[1:0]	{00}: No Response {01}: Latch-off {10}: Auto-Restart	
ISSC	Fault Response and Detection Frequency	ion Frequency?	0x22	0xA2 W/R_Byte	/R_Byte 0x00	bit[3:2]	Frequency Detection Threshold {00}: 50kHz {01}: 30kHz {10}: 40kHz {11}: 60kHz		
UVL Timer	UVL Fault Timer	8/16/32/64 msec	0x24	0xA4	W/R_Byte	0x03 (64 msec)	bit[1:0]	{00}: 8 msec {01}: 16 msec {10}: 32 msec {11}: 64 msec	
Watchdog Timer	Communication Rate Monitor	Disable/0.5 s/1 s/2 s	0х	x26	W/R_Byte	0x01 (0.5 sec)	bit[1:0]	{00}: No Watch-Dog {01}: 0.5 sec {10}: 1 sec {11}: 2 sec	
CVOL	Constant Voltage Mode Fault Response	Latch-off or AR or No Response?	0x28	0xA8	W/R_Byte	0x00	bit[1:0]	{00}: No Response {01}: Auto-Restart {10}: Latch-off	
CVOL Timer	Constant Voltage Fault Timer	8/16/32/64 msec	0х	:2A	W/R_Byte	0x00 (8 msec)	bit[1:0]	{00}: 8 msec {01}: 16 msec {10}: 32 msec {11}: 64 msec	
<del></del>		Writing a					bit[6]	Control Secondary	
		non-zero value					bit[5]	BPS Current Latch-off	
		enables interrupt					bit[4]	CVO Mode Peak load timer	
Interrupt	Interrupt Mask	Interrupt is	0x	2C	W/R_Byte	0x00	bit[3]	IS-pin Short	
		automatically disabled after					bit[2]		
		one interrupt					bit[1]	Vout(UV)	
		pulse sent out					bit[0]	Vout(OV)	
ОТР	Secondary Over- Temperature Fault Hysteresis	40°C/60°C	0x2E	0xAE	W/R_Byte	0x00	bit[0]	{0}: 40°C {1}: 60°C	

Table 2. Command Register Assignments (cont).

## **Telemetry (Read-Back) Registers Address Assignment and Description**

		Register Ad		Address					
	Name	Register Name	Address	Address with Odd Parity	Туре		Register Bit Assignments		
	READ0	Rev ID	0x00	0x80	R_Word	bit[15:0]	[Rev ID]		
						bit[15]	High Byte Parity		
	DEAD4			00	D 14/	bit[12:8]		(5, 6)	
	READ1	Output Voltage Set-Point	Ux	(02	R_Word	bit[7]	Low Byte Parity	- {Reg_CV}	
						bit[6:0]			
						bit[15]	High Byte Parity		
	DEADO	Lindow saltage Threehold	0	-04	D. Word	bit[8]		(Doc 11)/A)	
×	READ2	Undervoltage Threshold	UX	(04	R_Word	bit[7]	Low Byte Parity	- {Reg_UVA}	
Bac						bit[6:0]			
-pad						bit[15]	High Byte Parity		
r R	READ3	READ3 Overvoltage Threshold 0x06	,0¢	D. Word	bit[8]		(Dog. OVA)		
ste	KEAD3	Overvoltage Threshold	UX	(Ub	R_Word -	bit[7]	Low Byte Parity	- {Reg_OVA}	
egi						bit[6:0]			
Command Register Read-Back		VBUS Switch Enable				bit[14]	{Reg_VBEN}		
ша		Minimum Load		Minimum Load		bit[13]	{Reg_BLEEDER}		
E O	E	Turn PSU Off				bit[12]	{Reg_PSUOFF}		
	READ4	Fast VI Commands	0x08		R_Word	bit[11]	{Reg_FSTVIC}		
	NEAD I	Constant-Voltage Mode Only				bit[10]	{Reg_CVO}		
		Over-Temperature Fault Hysteresis				bit[9]	{Reg_OTP_HYS}		
		Cable Drop Compensation				bit[3:0]	{Reg_CDC}		
	READ5	Constant Current Set-Point	0.	:0A	R_Word	bit[15:8]	{Reg_CC}		
	KLADS	Constant Power Threshold	UX	WA	K_vvoiu	bit[7:0]	{Reg_VKP}		
		Overvoltage Fault				bit[15:14]	{Reg_OVL}		
မှ မွ		Undervoltage Fault					bit[13:12]	{Reg_UVL}	
me Sport		IS-pin Short				bit[9:8]	{Reg_ISSC}		
Programmed Fault Respose	READ6	Undervoltage Time Out	0x	(OC	R_Word	bit[7:6]	{Reg_UVLTIMER}		
rog		Watchdog Time Out	og Time Out			bit[5:4]	{Reg_WD_TIMER}		
- 2		CV Mode				bit[3:2]	{Reg_CVMODE}		
		CV Mode Timer				bit[1:0]	{Reg_CVTIMER}		
						bit[15]	High Byte Parity		
	READ7	Measured Output Current	0.	(0E	R_Word	bit[8]		Spec MEVELIBED 13	
	KLAD/	Measured Output Current	UX	UL	K_vvoiu	bit[7]	Low Byte Parity	- {Reg_MEASURED_I}	
¥						bit[6:0]			
ш Е						bit[15:12]	4'b0		
are							{Reg_MEASURED_V	}	
Measurement	READ9	Measured Output Voltage	0x12	<b>12</b>	R_Word	h:4[11.0]	Vout Range	Report-back resolution	
						bit[11:0]	3 - 7.2 V	20 mV	
							7.2 - 10 V	50 mV	
							10 - 20 V	100 mV	

Table 3. Telemetry (Read-Back) Register Assignments.

		Register	r Address					
Name	Description	Address	Address with Odd Parity	Туре			Register Name	
	Interrupt Enable					bit[15]	{Reg_INTERRUPT_EN}	
	System Ready Signal					bit[14]	{Reg_CONTROL_S}	
	Output Discharge					bit[13]	{Reg_VDIS}	
	Switching Frequency High?					bit[12]	{Reg_HIGH_FSW}	
READ10	Over-Temperature Protection Fault?					bit[9]	{Reg_OTP}	
(Instantaneous)	2% Bleeder Enabled	0>	(14	R_Word		bit[5]	{Reg_VOUT2PCT}	
	VOUTADC > 1.1*Vout					bit[4]	{Reg_VOUT10PCT}	
	IS-pin Short Circuit Detected					bit[3]	{Reg_ISSC}	
	Output Voltage UV Fault Comparator					bit[1]	{Reg_VOUT_UV}	
	Output Voltage OV Fault Comparator					bit[0]	{Reg_VOUT_OV}	
	CVO Mode AR					bit[15]	{Reg_ar _CV}	
-	IS-pin Short-Circuit AR					bit[12]	{Reg_ar_ISSC}	
	Output Voltage OV AR					bit[10]	{Reg_ar_VOUT_OV}	
	Output Voltage UV AR					bit[9]	{Reg_ar_VOUT_UV}	
	Latch-Off (LO) Occurred					bit[7]	{Reg_LO}	
READ11 (Latched)	CVO Mode LO	0x16	<b>α16</b>	R_Word		bit[6]	{Reg_Lo_CVO}	
(Laterica)	PSU Turn-Off CMD Received					bit[5]	{Reg_PSUOFF}	
	IS-pin Short-Circuit LO				bit[4]		{Reg_Lo_ISSC}	
	Output Voltage OV LO					bit[2]	{Reg_Lo_VOUT_OV}	
	Output Voltage UV LO					bit[1]	{Reg_Lo_VOUT_UV}	
	BPS-pin LO					bit[0]	{Reg_BPS_OV}	
					Mask	Status		
					bit[14]	bit[6]	{Reg_CONTROL_S}	
					bit[13]	bit[5]	{Reg_LO_Fault}	
READ12	Interrupte	0.	<b>α18</b>	R_Word	bit[12]	bit[4]	{Reg_CCAR}	
KLAD12	Interrupts	0,	(10	K_vvoiu	bit[11]	bit[3]	{Reg_ISSC}	
					bit[10]	bit[2]		
					bit[9]	bit[1]	{Reg_VOUT_UV}	
					bit[8]	bit[0]	{Reg_VOUT_OV}	
READ13	Average Output Current	0>	(1A	R_Word	bit	[15:12]	4b'0	
					b	it[11:0]	16 sample average of READ 9	
READ14	Average Output Voltage	0>	ά1C	R_Word		it[15:8]	8b'0	
						bit[7:0]	16 sample average of READ 7	
READ15	Voltage DAC	Ωx	κ5C	R_Word		it[15:8]	DAC_100mV	
	Totage DAC			••oiu		bit[7:0]	DAC_10mV	

Table 3. Telemetry (Read-Back) Register Assignments (cont.)

## **Command Registers**

#### **System Ready Status Register**

The system ready bit {Reg\_control\_s} must be read prior to the start of any I<sup>2</sup>C transactions and after the InnoSwitch3-Pro has entered into a reset state resulting from auto-restart (AR), latch-off (LO) or initial power-up.

When the {Reg\_control\_s} bit is set to "1", it means InnoSwitch3-Pro is ready to receive I<sup>2</sup>C commands.

To read the {Reg\_control\_s} bit, write the READ10 sub address 0x14 into the 0x80 address. Then read High Byte data back from address 0x80. The bit 14 is {Req\_control\_s}.

Constant current regulation is based on the average current measurement register (READ13).

For a 5 A CC threshold, the current sense resistor is 6.4 m $\Omega$ . The current limit step size for this example is 39.1 mA/step.

Example: For a power supply with maximum CC of 5 A (Rs = 6.4m $\Omega$ ), the following demonstrates changing the CC set point from 5 A to 2.5 A. This corresponds to change in CC from 100% (0x80) to 50% (0x40) – with odd parity this becomes 0x8040:

PI\_SLAVE\_ADDRESS [W]: 0x30 (8'b0011 0000)
PI\_Command: CC Register (0x98)
Low Byte: 0x40 (8'b0100 0000)
High Byte: 0x80 (8'b1000 0000)

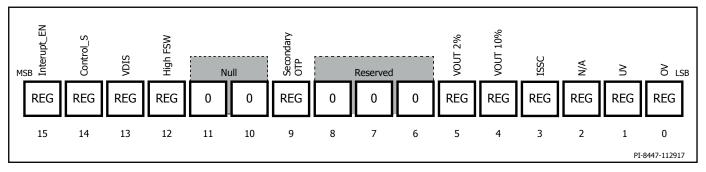


Figure 12. {Reg\_Control\_s} Telemetry Register.

Example: Reading the {Reg\_control\_s} bit:

PI\_SLAVE\_ADDRESS [W]: 0x30 (8'b0011 0000)

Read Register: 0x80

PI\_Command: READ10 (0x14), READ10 (0x14)

PI\_SLAVE\_ADDRESS [r]: 0x31 (8'b0011 0001)

# Programming Output Voltage (CV), Output Constant Current (CC), Constant Power Mode (CP), Cable Drop Compensation (CDC) and Constant Voltage Only Mode (CVO)

#### CV Register (0x10)

The output voltage of the power supply is regulated on the Vout-pin. The valid programming range is from 3 V to 24 V with 10 mV / lsb. The default CV register value is 5 V. Below 5 V and at light load below 50 mA, output monotonicity may not be visible with 10 mV / steps.

Example: to change CV from 5 V to 8 V

Convert 8 V to lsb representation: 8/(10mV/lsb) = 800

Convert to hex format (800 = 0x0320)

With odd parity bits added the hex data is 0x8620) The bit I<sup>2</sup>C command for this is shown below:

PI\_SLAVE\_ADDRESS [W]: 0x30 (8'b0011 0000)
PI\_Command: CV Register (0x10)
Low Byte: 0x20 (8'b0010 0000)
High Byte: 0x86 (8'b1000 0110)

This sequence of commands is shown in Figure 10 and Figure 23.

#### CC Register (0x98)

The constant current regulation register address is 0x18 and with odd parity it is 0x98. The constant current regulation threshold is adjustable from 20% (d'25) CC up to 100% (d'128) of the full scale. The full-scale constant-current threshold is set with the sense resistor between the IS and GND pins. The typical value for the full-scale current voltage drop is 32 mV ( $I_{\text{SV(TH)}}$ ). The resolution step size is (0.78%/step):

32 mV/128 = 0.25 mV/step/Rs

## Constant Output Power Voltage Threshold V<sub>KP</sub> (0x1A)

A constant output power characteristic is programmed via the "knee power voltage" in conjunction with the 100% constant current regulation threshold (full-scale current setting). If the full-scale CC is 2.5 A and the knee power voltage is set to 8 V, the constant power is 20 W. If the  $V_{_{\rm KP}}$  register were set to 12 V, the resultant constant power characteristic above the  $V_{_{\rm KP}}$  threshold would be 30 W.

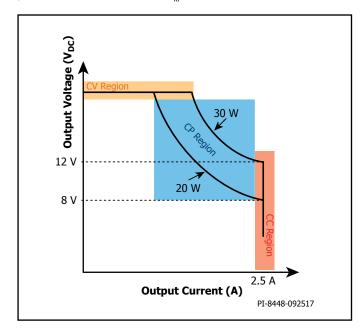


Figure 13. Constant Output Power Profile.

From no-load to heavy loading conditions, InnoSwitch3-Pro will operate in CV then transition into CP then into CC region below the  $V_{\kappa p}$  threshold. Setting  $V_{\kappa p}$  to maximum value (24 V) results in no Constant Output Power regulation region.

Example: To change  $V_{KP}$  from 24 V (d'240) (0xF0 = 0x0170 with odd parity) to 8 V (0x50 = 0x80D0):

PI\_SLAVE\_ADDRESS [W]: 0x30 (8'b0011 0000)
PI\_Command: VKP Register (0x1A)
Low Byte: 0xD0 (8'b1101 0000)
High Byte: 0x80 (8'b1000 0000)

Reducing the constant current regulation threshold does not modify the maximum programmed output power with a given  $V_{_{KP}}$  setting. From the example shown above, setting CC regulation to 2 A (full-scale CC is still 2.5 A), with  $V_{_{KP}}=8$  V, would result in output profile shown below with CP characteristic intercept of 10 V for the same 20 W constant power characteristic.

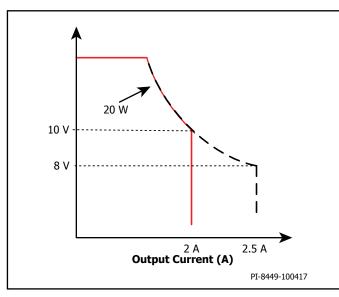


Figure 14. Constant Output Power Profile with Reduced CC Regulation Threshold.

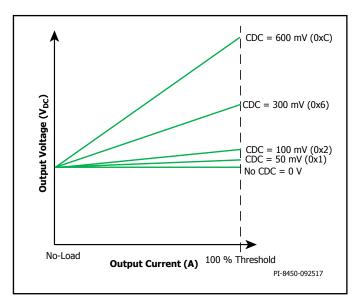


Figure 15. CDC as Function of Load Current.

#### Cable Drop Compensation (CDC) (0x16)

The amount of cable drop compensation has a controllable range of 0 V to 600 mV in 50 mV/steps. CDC is applied as a function of the current through the sense resistor (resistor between IS and GND pins) used to program the constant current regulation threshold. At no-load there is no CDC and the compensation is increased linearly as load increases and reaches the maximum programmed value at the onset of the 100% constant-current regulation threshold (full-scale voltage across the current sense resistor).

The table below shows the register values to program the desired CDC:

CDC (mV)	Hex Value	Binary
0	0x00	4'b0000
100	0x02	4'b0010
150	0x03	4'b0011
200	0x04	4'b0100
250	0x05	4'b0101
300	0x06	4'b0110
350	0x07	4′b0111
400	0x08	4'b1000
450	0x09	4'b1001
500	0x0A	4'b1010
550	0x0B	4'b1011
600	0x0C	4'b1100

Table 4. Cable Drop Compensation.

If the current sense resistor between IS pin to GND pin is shorted, there will be neither any cable drop compensation nor any constant current regulation.

Example: To change CDC from 0 V to 300 mV (0x06):

PI\_SLAVE\_ADDRESS [W]: 0x30 (8'b1011 0000)

PI\_Command: CDC Register (0x16)

Byte: 0x06 (4'b0110)

## Constant Voltage Only Mode (0x0E)

The InnoSwitch3-Pro can be programmed to operate with constant-voltage only and have no constant current regulation mode. The set output current register (0x98) sets the over-load threshold instead of regulating the constant current when the CVO mode is enabled. Once the load current exceeds the programmed current a peak load timer ( $t_{\rm PlT}$ ) is started. The options for the peak load timer (CVOL Timer Register 0x2A) are 8/16/32 and 64 ms. If the peak load exceeds the programmable timer, the InnoSwitch3-Pro can be programmed to respond to this fault as auto-restart, latch-off or no-response through the CVOL Register 0xA8. The default response for CVOL (CVO response) is no-response with 8 ms timer.

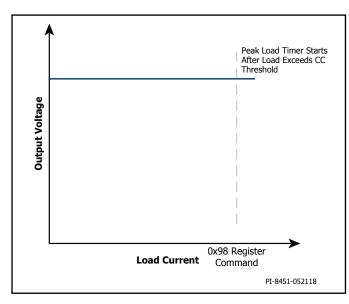


Figure 16. Constant Voltage Only (CVO) Mode.

Example: Enable CVO Mode, set  $t_{\rm PLT}$  to 16 msec and fault response to latch-off (LO):

PI\_SLAVE\_ADDRESS [W]: 0x30 (8'b0011 0000)
PI\_Command: CVO Register (0x0E)

Byte: 0x01 (1'b1)

 PI\_SLAVE\_ADDRESS [W]:
 0x30 (8'b0011 0000)

 PI\_Command:
 CVOL Timer Register (0x2A)

Byte: 0x01 (2'b01)

PI\_SLAVE\_ADDRESS [W]: 0x30 (8'b0011 0000)
PI\_Command: 0x30 (8'b0011 0000)
CVOL Register (0xA8)

Byte: 0x02 (2'b10)

The output undervoltage protection mode discussed in Output Overvoltage and Undervoltage Protection Thresholds/Fault Behavior section is still active in the CVO mode of operation even if the individual UV fault response is set to 'No response'. The following control flow-chart shows the expected behavior of the device under the different potential programming scenarios.

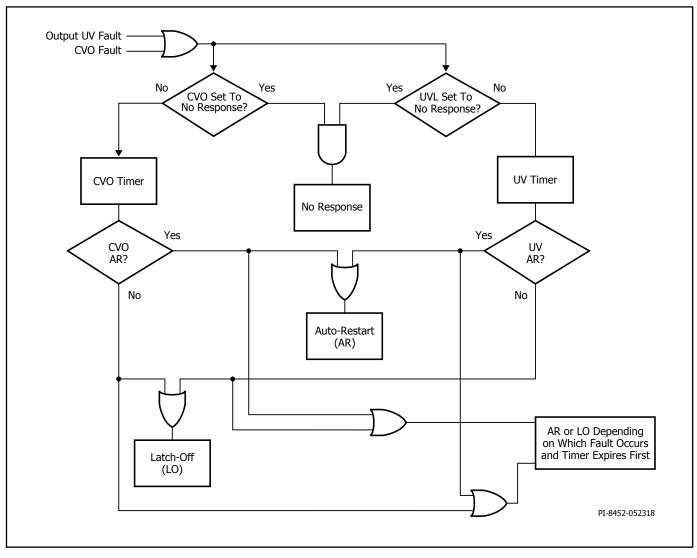


Figure 17. CVO and Output UV Control.

#### **Programmable Protection Mechanisms**

#### Output Overvoltage and Undervoltage Protection Thresholds/Fault Behavior

Besides the ability of programing the OV/UV thresholds on the fly as a function of the set CV, the behavior of the power supply once a fault occurs (a. No-Fault which just sets the fault register, b. Auto-restart (AR) or c. Latch-off (LO) the power supply) and timing for the UV fault detection (8 to 64 msec) is programmable as well. The output overvoltage delay is fixed at  ${\sim}80~\mu s$ . All faults that are programmed to have no-fault respose will be logged into the telemetry read-back fault register. Since the minimum UV setting is 3 V, the response should be set to no-response for 3 V operation.

 $\mathsf{OVA}(\mathsf{0x92})$ : write to this address to specify the overvoltage

threshold

UVA(0x94) : write to this address to specify the undervoltage

threshold

OVL(0x1C) : write to this address to specify the behavior to OV fault UVL(0x9E) : write to this address to specify the behavior to UV fault UVL Timer(0xA4) : write to this register specify the UV timer

Example: To change the absolute output undervoltage threshold 3 V (d'30) (0x809E with odd parity) fault response to latch-off (LO) (0x01) and configure fault timer to 64 msec (0x03):

 PI\_SLAVE\_ADDRESS [W]:
 0x30 (8'b0011 0000)

 PI\_Command:
 UVA Register (0x94)

 Low Byte:
 0x9E (8'b1001 1110)

 High Byte:
 0x80 (8'b1000 0000)

 PI\_SLAVE\_ADDRESS [W]:
 0x30 (8'b0011 0000)

 PI\_Command:
 UVL Register (0x9E)

 Byte:
 0x01 (2'b01)

PI\_SLAVE\_ADDRESS [W]: 0x30 (8'b0011 0000)
PI\_Command: UVL Timer Register (0xA4)

Byte: 0x03 (2'b11)

IS Pin Short-Circuit Fault Protection

The InnoSwitch3-Pro can be configured to monitor whether a short-circuit fault occurs across the output current sense resistor or a short-circuit fault across the IS to GND pins.

A fault is annunciated in the event the IS pin voltage does not exceed approximately 50% of the full constant-current threshold (IS $_{\text{V(TH)}}$ ) with a switching frequency exceeding a programmed threshold. The switching frequency can be selected in a range from 30 to 60 kHz. This must be carefully selected to suit the expected operating conditions of the design.

An IS pin short (ISSC) can be programmed to have a response to be a. No-fault, b. Auto-restart (AR) or c. Latch-off (LO). In the event the behavior is a No-fault, the Telemetry Read-Back Fault Register is logged.

 $\ensuremath{\mathsf{ISSC}}(0x\ensuremath{\mathsf{A2A}})$  : write to this address to specify the behavior for an IS-GND short.

Example: To set the behavior of an IS pin short to AR for switching frequency exceeding 40 kHz. (4'b10 10 = 0x10):

PI\_SLAVE\_ADDRESS [W]: 0x30 (8'b0011 0000)
PI\_Command: ISSC register (0xA2)
Byte: 0x10 (4'b1010)

## Watchdog Timer (0x26)

The Watchdog timer supervises the communication on the  $I^2C$  command lines and has an adjustable time-out. InnoSwitch3-Pro will go into a reset state if  $I^2C$  commands are not received within the programmable time interval. The watchdog timer does not engage

until the master issues the first  $I^2C$  command (Read or Write). In the reset state the following occurs:

- 1. VBUS Switch is Disabled (Series switch is open).
- 2. VOUT pin voltage regulates at the default 5 V threshold.
- 3. All command Registers are cleared.

By writing 0x00 into register 0x26, the Watchdog timer is disabled. Disabling this feature can be useful in initial software debugging or checking functionality of the device on the bench.

Example: To disable the Watchdog timer:

PI\_SLAVE\_ADDRESS [W]: 0x30 (8'b0011 0000)

PI\_Command: Watchdog Timer Register (0x26)

Byte: 0x00 (2'b00)

#### Opening and Closing the Series VBUS Switch (0x04)

Enabling VBEN (closing the VBUS Series Switch) speeds up the ADC sampling frequency in order to achieve high control accuracy. Write commands cannot be accepted faster than 80 msec when the VBEN is disabled (Series VBUS Switch open).

Write 0x03 (with odd parity this becomes 0x8083) into the VBEN register (0x04) to close the series VBUS Switch and write 0x00 to this register to open the switch. When the VBUS switch is open (VBEN disabled), the system is reset to the default output voltage set point of 5 V. Disabling the series VBUS switch also resets all the programmable command registers to their default values. The InnoSwitch3-Pro controller is in a state of reset when VBEN is disabled or the VDIS register is enabled. For both these commands, since the controller is in reset, an ACK or Nack at the end of the command should not be expected.

Enabling the VBEN register automatically disables the VDIS register (0x08) described in Active VOUT Pin Bleeder and Output Load Discharge Functions section.

Example: Enabling (Closing) the Series VBUS Switch (0x8083):

PI\_SLAVE\_ADDRESS [W]: 0x30 (8'b0011 0000)
PI\_Command: VBEN Register (0x04)
Byte: 0x83 (8'b1000 0011)

Prior to sending command to open the series bus switch, a command to set the output voltage (CV registor 0x10) to 5 V is recommended. In the event of an auto-restart or latch-off, the bus switch is not disabled.

#### Turn-Off the Power Supply (0x8A)

The I<sup>2</sup>C master has the ability to turn-off the power supply (through an I<sup>2</sup>C command), which will require AC power cycling to restart the power supply.

Example: Turn-off the power supply:

PI\_SLAVE\_ADDRESS [W]: 0x30 (8'b0011 0000)

PI\_Command: Turn-Off PSU Register (0x8A)

Byte: 0x01 (1'b1)

#### **Fast VI Command**

By default, the maximum speed in which CV (0x10) and CC (0x98) commands can be sent to program output voltage/current respectively is 10 msec. However, the speed limit can be removed by setting 0x1 to the Fast VI Command Register (0x8C).

Example: To disable speed limit for  $\emph{V/I}$  commands:

PI\_SLAVE\_ADDRESS [W]: 0x30 (8'b0011 0000)

PI Command: Fast VI Speed Register (0x8C)

Byte: 0x01 (1'b1)

#### Active VOUT Pin Bleeder and Output Load Discharge Functions

There may be circumstances where the VOUT pin strong bleeder function must be activated to discharge the output voltage from a high to low regulation set point.

The VOUT bleeder can be activated by writing 0x01 into BLEEDER Register (0x86).

The BLEEDER register must not be enabled for extended period of time to prevent excessive power dissipation in the controller. When the BLEEDER function is being used to bleed the output voltage from high to low set point, the status of the  $\rm V_{OUT}10PCT$  register (bit 4 in the READ10 0x14 read register) should be used to disable the function. The VOUT10PCT register is set once the output voltage is above 10% of the target regulation voltage. The 2% Bleeder Enabled Register, READ10 (0X14) bit 5 can be used instead of the VOUT10PCT to determine when the BLEEDER register should be disabled for no-load transients from high to low output voltage transitions.

The InnoSwitch3-Pro automatically activates a weak current bleeder (>5mA) on the VOUT pin until the output voltage settles to less than 2% of the set regulation threshold.

The InnoSwitch3-Pro can also discharge the VBUS output voltage by bringing the VB/D pin to ground. The discharge circuit is a series diode + resistor tied from the VBUS output to the VB/D pin shown in the typical application schematic. Load discharge function can be activated by writing 0x03 (0x8083 with odd parity) into VDIS register (0x08).

Enabling the VDIS register will automatically disable the VBEN register (0x04) and reset the device to the default state.

The I<sup>2</sup>C master can use telemetry to monitor the VOUT pin voltage or a fixed timer to help determine when to disable both these functions.

Example: Activate the Vout Bleeder:

PI\_SLAVE\_ADDRESS [W]: 0x30 (8'b0011 0000)
PI\_Command: BLEEDER Register (0x86)
Byte: 0x01 (1'b1)

Example: Discharge the VBUS Output:

PI\_SLAVE\_ADDRESS [W]: 0x30 (8'b0011 0000)
PI\_Command: VDIS Register (0x08)
Byte: 0x83 (8'b1000 0011)

## **Secondary Over-Temperature Protection (0xAE)**

As the secondary controller die temperature increases beyond  $\sim\!125$  °C, the active VOUT pin bleeder function described above will be turned off. The bleeder will not be permitted to be re-enabled until the controller temperature falls below the programmable hysteresis value.

Example: Set Secondary OTP Hysteresis to 60 °C:

PI\_SLAVE\_ADDRESS [W]: 0x30 (8'b0011 0000)
PI\_Command: 0TP Register (0xAE)

Byte: 0x01 (1'b1)

#### **Transient Response**

If faster transient response is required in the application the InnoSwitch3-Pro includes command registers to reduce the time for low to high output voltage transitions. The command register addresses and recommended settings are shown in the table below:

Command Register Address	Def	ault	Recommended for Speed Up		
Register Address	MSB	LSB	MSB	LSB	
0x32	0x28	0x1E	0x14	0x0A	
0x34	0x08	0xC8	0x0F	0x84	

Using values other than the default or recommended settings about could lead to oscillatory behavior.

#### **Constant Voltage Load**

The constant current regulation mode in the InnoSwitch3-Pro can be optimized for constant voltage (CV) type load if this is required by the end application. Enabling this command register reduces the output current ripple for CV load only. The command register and setting below should only be used if CV load must be supported.

Command Register Address	Def	fault	Recommended for CV Load	
Register Address	MSB	LSB	MSB	LSB
0x30		0x20		0x80

## **Telemetry (Read-back) Registers**

Telemetry read registers (READ1 to READ6) show the content of all the command registers in Table 2.

#### **Fault Registers**

All the command registers including set voltage, set current, constant-power knee voltage, control (Series VBUS Switch, VOUT pin Bleeder, Load discharge etc.) and all fault status can be read-back using the Telemetry functionality of the InnoSwitch3-Pro through I<sup>2</sup>C.

The READ10 telemetry registers are instantaneous and are cleared whenever the condition is no longer valid.

The READ11 (0x16) Register contains fault register data for autorestart and latch-off. This register is only cleared when the BPS pin falls below its undervoltage threshold or the series VBUS switch is opened.

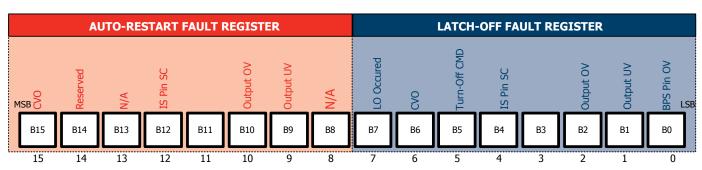


Figure 18. READ11 Fault Telemetry Register Assignments.

PI-8453-120717

Example: Read the Fault Telemetry Register to determine an autorestart occurred due to an output undervoltage (UV) Fault:

PI\_SLAVE\_ADDRESS [W]: 0x30 (8'b0011 0000)

Read Register: 0x80 Telemetry Register: 0x16, 0x16

PI\_SLAVE\_ADDRESS [r]: 0x31 (8'b0011 0001)

PI\_Slave Response: Low Byte 8'b0000 0000 (0x00) High Byte 8'b0000 0010 (0x02)

Refer to Figure 11 and Figure 24 that illustrates this read sequence.

Type of Fault	High-Byte	Low-Byte
Auto-Restart: CVO Mode	0x80	0x00
Auto-Restart: IS pin Short-Circuit	0x10	0x00
Auto-Restart: Output Voltage OV	0x04	0x00
Auto-Restart: Output Voltage UV	0x02	0x00

Table 5. Summary of Telemetry Fault Codes.

#### **Main Regulation DAC Input**

The READ15 telemetry register is the input into the main regulation loop that controls constant voltage, constant current and constant output power regulation. If this register is the same as the Set CV Register (0x10) the converter is operating in constant-voltage mode. If the READ15 is less than the Set CV Register (0x10) the converter is operating in constant-current (CC) or constant-power (CP) mode depending on the value of the Constant Power Knee Voltage Register (0x1A).

The output voltage from the READ15 register is computed as  $V_{\text{OUT}}$  = 5 V + (MSB  $\times$  100 mV) – (LSB x 10 mV).

Example: READ15 (0x5C): MSB = 0x00, LSB = 0x0E LSB is d'14 so the computed  $V_{OLT} = 5 - (14 \times 10 \text{ mV}) = 4.86 \text{ V}$ 

#### **Fault Signaling Interrupt Through SCL Pin**

In order to improve the fault reporting, an active interrupt reporting scheme is featured on the SCL pin during  $I^2C$  idle state (when both SDA and SCL pins are pulled high).

When a fault occurs, the SCL pin will behave in one of the following two conditions:

1. When the SCL pin is in idle mode (see Figure 19), the fault interrupt will happen as soon as the fault is detected. The interrupt pulls down the SCL pin for 50  $\mu$ sec then releases it back to HI State.

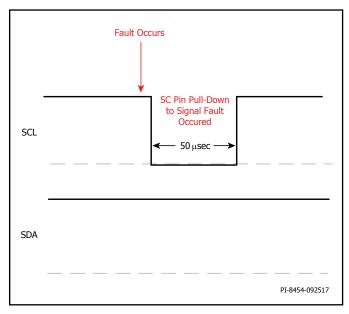


Figure 19. Interrupt Mask During Idle I<sup>2</sup>C.

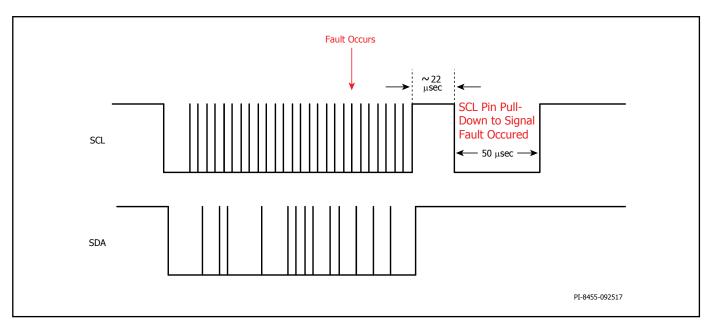


Figure 20. Interrupt Mask During Active I<sup>2</sup>C Transaction.

2. When the SCL pin is busy (active  $I^2C$  transaction) (see Figure 20), the fault interrupt will wait for the  $I^2C$  transaction to be completed, wait  $\sim\!22~\mu sec$  and then pull down the SCL line for 50  $\mu sec$  (minimum) then releases it back to HI State.

The Interrupt Mask Write Register (0x2C) must be enabled for each of the individual fault conditions shown below in order to activate this feature. Once a fault occurs, the Interrupt Mask is reset and the particular faults of interest must be re-enabled to activate the SCL reporting scheme. The Control Secondary Interrupt (Bit 6) is an indication that the secondary controller is waiting to handshake with primary. Several system faults could trigger this event such as primary-side thermal shutdown or an input line under or overvoltage condition.

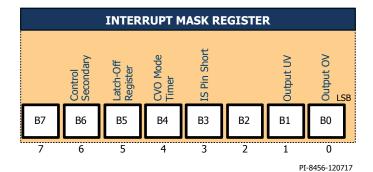


Figure 21. Interrupt Mask Register.

Example: Set the Interrupt Write Register to flag SCL pin fault for output OV, UV or short-circuit only:

PI\_SLAVE\_ADDRESS [W]: 0x30 (8'b0011 0000)
PI\_Command: INTM Register (0x2C)
Byte: 0x07 (8'b0000 0111)

## **Output Voltage Measurement**

The voltage on the VOUT pin is available on the Telemetry Register READ 9 (0x12). The tolerance of this telemetry register is  $\pm 5\%$  over the entire regulation range of 3 to 24 V.

When the output voltage is below 5 V at loads below  $\sim 50$  mA, the read back voltage may fluctuate due to very low switching frequency of the converter. This is normal and expected behavior.

The output voltage report back is in 12-bit format but the resolution depends on the output voltage range as shown in Table 6. This telemetry register is for indication only, in steady-state operation the VOUT pin is very tightly regulated per the CV Write Register (0x10) discussed in CV Register (0x10) section.

The report back resolution step size depending on output voltage is tabulated below:

Output Volta	Resolution Step Size	
3	7.2	20 mV
7.2	10	50 mV
10	24	100 mV

Table 6. Output Voltage Report Back Resolution.

If the actual output voltage is 5.11 V (CV Write Register 0x10 set to 0x837F.)

The READ9 register will be at  $5.10~\rm V$  or  $5.12~\rm V$  since the resolution step size is  $20~\rm mV$  in this range

Example: If the READ 9 read-back register value is 0xA801 recalling that low byte precedes the high byte, the proper hex to decimal conversion would be from 0x01A8 = 424 in decimal.

The full output voltage range the report back should be divided by 10 mV to convert into actual output voltage, which in this example results in an output voltage of 4.24 V.

Read-back of the output voltage set-point READ1 (0x02) as with all the read registers is formatted with low-byte preceding the high-byte.

#### **Output Current Measurement**

The load output current is also available on the Telemetry Register.

Telemetry Register READ7 (0x0E) contains the measured relative output load current data. The load current is available on a relative basis with respect to the full-scale constant current regulation threshold programmed by the sense resistor tied between the IS and GND pin of the InnoSwitch3-Pro.

The ADC full range is 128, which denotes 100% threshold across the current sense resistor.

The accuracy of the output current read-back is tightest at full scale and decreases as the voltage threshold across the current sense resistor decreases as shown in Figure 22.

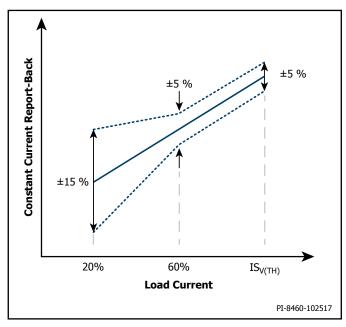


Figure 22. Constant-Current Report Back Tolerance.

Example: If a 16 m $\Omega$  sense resistor is used and the read-back register is 0x8040.

Removing the odd parity bit from high byte results in 0x40 = 64 in decimal.

Sensed current value = N (decimal)  $\times$  0.25/ $R_{SENSE}$ . 64  $\times$  0.25/16 = 1A. This is the measured output current value:

(0.25 mV = 32 mV/128, where 32 mV ( $I_{\text{SV(TH)}}$ ) is the full range R voltage, 128 is the ADC full range).

The READ13 and READ14 are 16 sample rolling averages of the measured output current and output voltage respectively. The value of these average registers is more stable than the instantaneous registers (READ7 and READ9) but take slightly longer to stabilize. When the series BUS switch is opened these registers are cleared and values are reset to zero until the measurement start to accumulate. The resolution of READ 13 and READ 14 is the same as the READ7 and READ 9 respectively.

The output voltage and current measurement registers are updated every 100  $\ensuremath{\mu s}.$ 

#### I<sup>2</sup>C Connection

#### **uVCC External Power Supply**

The uVCC pin provides an accurately regulated 3.6 V supply to an external controller. The maximum load current capability of this supply is 50 mA ( $I_{\mbox{\tiny UVCC}}$ )for 0.5 seconds when the VOUT pin is greater than or equal to 5 V. For steady-state operation, it is expected the current drawn from uVCC is less than 10 mA. The uVCC pin should be decoupled to the GND pin with at least a 2.2  $\mu F$  ceramic capacitor. When the VOUT pin voltage is less than 3.9 V, the internal LDO will droop and follow VOUT pin voltage. Under these conditions, the uVCC pin voltage is dependent on load current and internal series impedance. At VOUT pin = 3 V and 6 mA load current on uVCC, the expected output on uVCC will be  $\sim\!\!2.85$  V (3 V - 24  $\Omega$  x 6 mA).

If the VOUT pin voltage falls sufficiently to cause the uVCC pin to go below the  $\rm uVCC_{RST}$  threshold, communication through  $\rm I^2C$  is no longer available.

#### **SCL/SDA Pull-up Requirements**

The SCL and SDA-pins should be pulled-up to the uVCC pin with a resistor. The maximum pull-up resistance is dependent on the capacitance of the SCL/SDA pins and  $\rm I^2C$  Master. The resultant voltage fall-time to the V $_{\rm IL}$  threshold assuming a total capacitance of 20 pF is tabulated as function of SCL clock frequency in the table below.

Max Frequency (kHz)	Max Pull-Up Resistance (kΩ)	t <sub>F</sub> (ns)
400	13	300
500	10	240
600	8	200
700	7	178

Table 7. I<sup>2</sup>C Pull-Up Resistor Values.

## I<sup>2</sup>C Example Waveforms Setting The Output Voltage To 8 V

Same as Example shown in Figure 10.

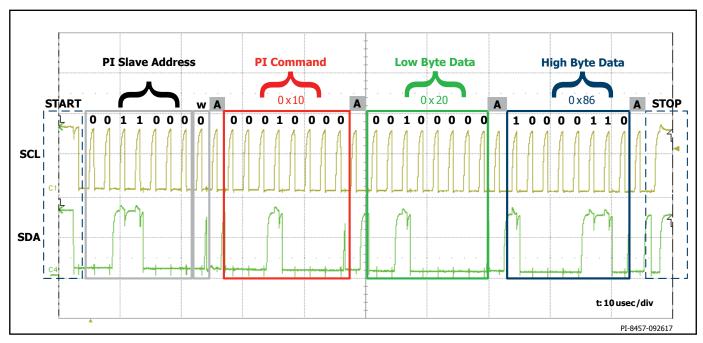


Figure 23. I<sup>2</sup>C Waveforms for Setting Output Voltage to 8 V.

## Reading Telemetry Fault Register After AR Event Caused by Undervoltage

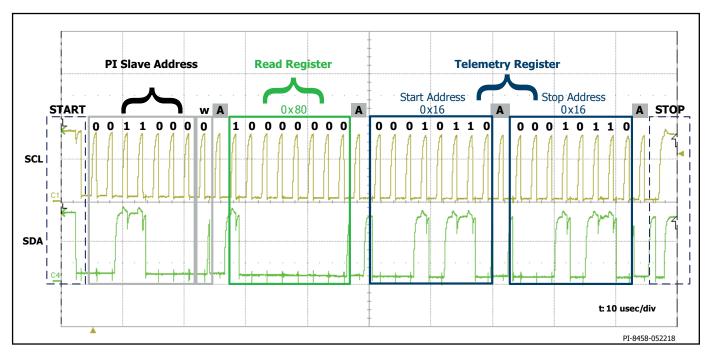


Figure 24. I<sup>2</sup>C Waveforms for Writing Address of Fault Register READ11 in Read Register (READ0) in Order to Read Back READ11.



Figure 25. I<sup>2</sup>C Waveforms for Read Value From READ11 Register.

## **Applications Example**

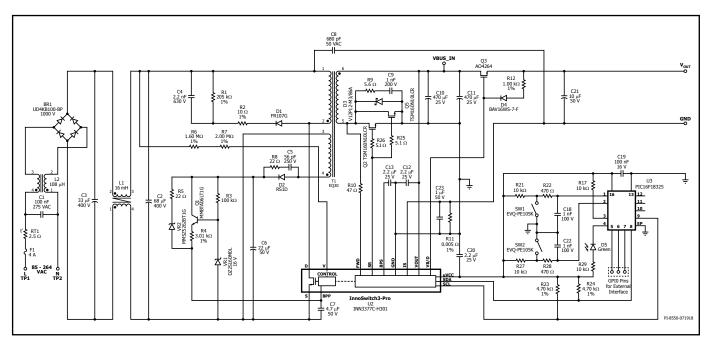


Figure 26. 3 V - 8 V, 5 A; 8 V - 20 V Constant Power 40 W Programmable Power Supply.

The circuit shown in Figure 26 is a 3 V - 8 V, 5 A; 8 V - 20 V constant power 40 W programmable power supply using the INN3377C IC. The power stage is controlled by a general purpose PIC16F18325 microcontroller. This design features DOE Level 6 and EC CoC 5 compliance.

Common mode choke L1 and L2 provides attenuation for EMI. Bridge rectifier BR1 rectifies the AC line voltage and provides a full wave rectified DC. Thermistor RT1 limits the inrush current when the power supply is connected to the input AC supply. Fuse F1 isolates the circuit and provides protection from component failure.

One end of the transformer primary is connected to the rectified DC bus; the other end is connected to the drain terminal of the integrated MOSFET in the InnoSwitch3-Pro IC (U1).

A low-cost RCD clamp formed by diode D1, resistors R1, R2 and capacitor C4 limits the peak Drain voltage of U1 at the instant of turn-off of the MOSFET inside U1. The clamp helps to dissipate the energy stored in the leakage reactance of transformer T1.

The InnoSwitch3-Pro IC is self-starting, using an internal high-voltage current source to charge the PRIMARY BYPASS pin capacitor (C7) when AC is first applied. During normal operation, the primary-side block is powered from an auxiliary winding on the transformer T1. Output of the auxiliary (or bias) winding is rectified using diode D2 and filtered using capacitor C6. Resistors R3 and R4 along with Q1 and VR1 form a linear regulator circuit to limit the current being supplied to the PRIMARY BYPASS pin of the InnoSwitch3-Pro IC (U1) irrespective of the output voltage. The Zener diode VR2 along with resistor R5 provides latching OVP in the event of an output overvoltage condition.

In a flyback converter, output of the auxiliary winding tracks the output voltage of the converter. In the event of an overvoltage at the output of the converter, the auxiliary winding voltage increases and causes breakdown of VR2. This causes a current to flow into the PRIMARY BYPASS pin of InnoSwitch3-Pro IC (U1). If the current flowing into the PRIMARY BYPASS pin increases above the  $\rm I_{sp}$  threshold,

the InnoSwitch3-Pro IC controller will latch-off and prevent any further increase in output voltage.

The secondary-side of the InnoSwitch3-Pro IC provides output voltage and output current sensing along with drive to a MOSFET providing synchronous rectification. The secondary output of the transformer is rectified by MOSFETs Q2, Q5 and filtered by capacitors C10 and C11. High frequency ringing during switching transients that would otherwise create radiated EMI, is reduced via a RC snubber, R9 and C9. Current sharing of the two FETs Q2 and Q5 are obtained by adding the resistors R25 and R26 in series with the gates of the respective FETs.

The gate of Q2 and Q5 are turned on by secondary-side controller inside IC U1, based on the winding voltage sensed via resistor R10 and fed into the FORWARD pin of the IC.

In continuous conduction mode of operation, the MOSFET is turned off just prior to the secondary-side requesting the start of a new switching cycle from the primary. In discontinuous or continuous mode of operation, the power MOSFET is turned off when the voltage drop across the MOSFET falls below a threshold of  $V_{\text{SR(TH)}}$ . Secondary-side control of the primary-side power MOSFET avoids any possibility of cross conduction of the two MOSFETs and provides extremely reliable synchronous rectification.

The secondary-side of the IC is self-powered from either the secondary winding forward voltage or the output voltage. Capacitor C13, connected to SECONDARY BYPASS pin of InnoSwitch3-Pro IC (U1) provides decoupling for the internal circuitry. Capacitor C12 is needed between the VOUT pin and the SECONDARY GROUND pin for ESD protection of the VOUT pin.

During CC operation, when the output voltage falls, the device will power itself from the secondary winding directly. During the on-time of the primary-side power MOSFET, the forward voltage that appears across the secondary winding is used to charge the SECONDARY BYPASS pin decoupling capacitor C13 via resistor R10 and an internal

## InnoSwitch3-Pro

regulator. This allows output current regulation to be maintained down to the minimum auto-restart threshold set by the  $\rm I^2C$  interface. Below this level the unit enters auto-restart until the output load is reduced

Output current is sensed by monitoring the voltage drop across resistor R11 between the IS and SECONDARY GROUND pins. A threshold of approximately 32 mV reduces losses. A decoupling capacitor C23 is needed between the IS and SECONDARY GROUND pin to improve CC accuracy. Once the internal current sense threshold is exceeded, the device regulates the number of switch pulses to maintain a fixed output current.

When the output current is below the CC threshold, the device operates in constant voltage mode. The output voltage is set by the  $\rm I^2C$  interface.

The PIC microcontroller gets its supply through the  $\mu VCC$  pin of InnoSwitch3-Pro. Switch1 (SW1) increments output voltage while Switch2 (SW2) decrements output voltage. Such a design is used in a system where output voltage is required to be controlled through an external interface.

The PIC microcontroller communicates over its  $I^2C$  lines to the SDA and SCL pins (which are both 3.3 V and 5 V compatible) of the InnoSwitch3-Pro IC. The SDA and SCL lines need pull-up resistors R24 and R23 respectively to the  $\mu$ VCC pin. The  $\mu$ VCC pin needs a decoupling capacitor C20.

N-MOSFET Q3 forms the bus switch and is controlled by the VB/D pin on the InnoSwitch3-Pro IC. Resistor R12 and diode D4 are needed from the Source of the MOSFET to its gate for providing a voltage discharge path when the bus switch is opened. Capacitor C21 is needed at the output for ESD protection.

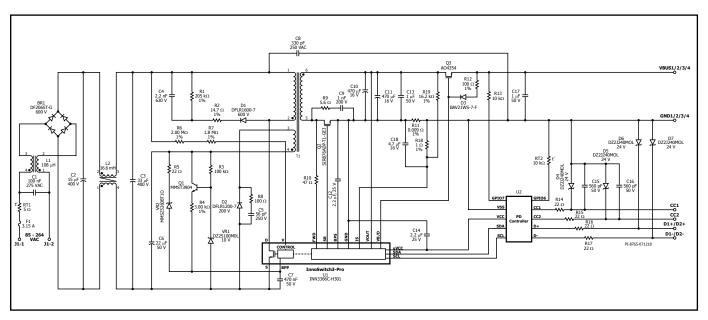


Figure 27. 5 V / 3 A; 9 V / 3 A; 3 V – 11 V PPS USB PD 3.0 Compliant Adapter.

The circuit shown in Figure 27 is a 5 V / 3 A; 9 V / 3 A; 3 V - 11 V PPS USB PD 3.0 compliant adapter using INN3366C IC. The power stage is controlled by a USB PD controller. This design features DOE Level 6 and EC CoC 5 compliance.

Common mode choke L1 and L2 provides attenuation for EMI. Bridge rectifier BR1 and BR2 rectify the AC line voltage and provides a full wave rectified DC. Thermistor RT1 limits the inrush current when the power supply is connected to the input AC supply. Fuse F1 isolates the circuit and provides protection from component failure. Thermistor RT1 limits the inrush current when the power supply is connected to the input AC supply.

One end of the transformer primary is connected to the rectified DC bus; the other end is connected to the drain terminal of the integrated MOSFET in the InnoSwitch3-Pro IC (U1).

A low-cost RCD clamp formed by diode D1, resistors R1 and R2 and capacitor C4 limits the peak Drain voltage of U1 at the instant of turn-off of the MOSFET inside U1. The clamp helps to dissipate the energy stored in the leakage reactance of transformer T1.

The InnoSwitch3-Pro IC is self-starting, using an internal high-voltage current source to charge the PRIMARY BYPASS BPP pin capacitor (C7) when AC is first applied. During normal operation, the primary-side block is powered from an auxiliary winding on the transformer T1. Output of the auxiliary (or bias) winding is rectified using diode D2 and filtered using capacitor C6. Resistor R3 and R4 along with Q1 and VR1 form a linear regulator circuit to limit the current being supplied to the PRIMARY BYPASS pin of the InnoSwitch3-Pro IC (U1) irrespective of the output voltage. The Zener VR2 along with resistor R5 provides latching OVP in the event of an output overvoltage condition.

In a flyback converter, output of the auxiliary winding tracks the output voltage of the converter. In the event of an overvoltage at the output of the converter, the auxiliary winding voltage increases and causes breakdown of VR2. This causes a current to flow into the

PRIMARY BYPASS pin of InnoSwitch3-Pro IC (U1). If the current flowing into the PRIMARY BYPASS pin increases above the  $\rm I_{sD}$  threshold, the InnoSwitch3-Pro IC controller will latch-off and prevent any further increase in output voltage.

The secondary-side of the InnoSwitch3-Pro IC provides output voltage and output current sensing along with drive to a MOSFET providing synchronous rectification. The secondary output of the transformer is rectified by MOSFET Q2 and filtered by capacitors C10 and C11. High frequency ringing during switching transients that would otherwise create radiated EMI, is reduced via a RC snubber, R9 and C9.

The gate of Q2 is turned on by secondary-side controller inside U1, based on the winding voltage sensed via resistor R10 and fed into the FORWARD pin of the IC.

In continuous conduction mode of operation, the MOSFET is turned off just prior to the secondary-side requesting the start of a new switching cycle from the primary. In discontinuous or continuous mode of operation, the power MOSFET is turned off when the voltage drop across the MOSFET falls below a threshold of  $V_{\text{SR(TH)}}$ . Secondary-side control of the primary-side power MOSFET avoids any possibility of cross conduction of the two MOSFETs and provides extremely reliable synchronous rectification.

The secondary-side of the IC is self-powered from either the secondary winding forward voltage or the output voltage. Capacitor C12, connected to the SECONDARY BYPASS BPS pin of InnoSwitch3-Pro IC U1 provides decoupling for the internal circuitry. Capacitor C13 is needed between the VOUT pin and the SECONDARY GROUND pin for ESD protection.

During CC operation, when the output voltage falls, the device will power itself from the secondary winding directly. During the on-time of the primary-side power MOSFET, the forward voltage that appears across the secondary winding is used to charge the SECONDARY BYPASS decoupling capacitor C12 via resistor R10 and an internal

## InnoSwitch3-Pro

regulator. This allows output current regulation to be maintained down to the minimum auto-restart threshold set by the  $\rm I^2C$  interface. Below this level the unit enters auto-restart until the output load is reduced.

Output current is sensed by monitoring the voltage drop across resistor R11 between the IS and SECONDARY GROUND pins. A threshold of approximately 32 mV reduces losses. Once the internal current sense threshold is exceeded, the device regulates the number of switch pulses to maintain a fixed output current.

Below the CC threshold, the device operates in constant voltage mode. The output voltage is set by the  $I^2C$  interface.

In this design, (U2) is the USB PD controller. It gets its supply from the  $\mu VCC$  pin of the InnoSwitch3-Pro IC. Output voltage requests are sent by the IC (U2) to InnoSwitch3-Pro through the I²C communication lines (SDA and SCL) when sink requests for the same. The  $\mu VCC$  pin needs a decoupling capacitor C14.

USB PD protocol is communicated over either CC1 or CC2 line depending on the orientation in which the Type-C plug is connected.

N-MOSFETS Q3 and Q4 form the bus switch and make the USB Type-C receptacle cold socket when no device is attached to the charger as per the USB Type-C specification. Resistor R12 and diode D3 are needed from the Source of the MOSFET to the gate for providing a voltage discharge path when the bus switch is opened. Capacitor C17 is needed at the output for ESD protection.

## **Key application Considerations**

#### **Output Power Table**

The data sheet output power table (Table 1) represents the maximum practical continuous output power level that can be obtained under the following assumed conditions:

- The minimum DC input voltage is 90 V or higher for 85 VAC input, or 220 V or higher for 230 VAC input or 115 VAC with a voltagedoubler. The value of the input capacitance should be sized to meet these criteria for AC input designs.
- Efficiency assumptions depend on power level. Smallest device assumes efficiency >84% and increases to efficiency >89% for the largest device.
- 3. Transformer primary inductance tolerance of  $\pm 10\%$ .
- 4. Reflected output voltage  $(V_{OR})$  is set to maintain  $K_p = 0.8$  at minimum input voltage conditions for universal line and  $K_p = 1$  for high input line conditions.
- Maximum conduction losses for adapter ratings is limited to 0.6 W and 0.8 W for open frame.
- Increased current limit is selected for peak and open frame power columns and standard current limit for adapter columns.
- The part is board mounted with SOURCE pins soldered to a sufficient area of copper and/or a heat sink is used to keep the SOURCE pin temperature at or below 110 °C.
- Ambient temperature of 50 °C for open frame designs and 40 °C for sealed adapters.

\*Below a value of 1,  $K_p$  is the ratio of ripple to peak primary current. To prevent reduced power delivery, due to premature termination of switching cycles, a transient  $K_p$  limit of  $\geq 0.25$  is recommended. This prevents the initial current limit ( $I_{\text{INT}}$ ) from being exceeded at MOSFET turn-on.

#### Primary-Side Overvoltage Protection (Latch-Off Mode)

The primary-side output overvoltage protection provided by the InnoSwitch3-Pro IC uses an internal latch that is triggered by a threshold current of  $\rm I_{SD}$  into the PRIMARY BYPASS pin. In addition to an internal filter, the PRIMARY BYPASS pin capacitor forms an external filter providing noise immunity from inadvertent triggering. For the bypass capacitor to be effective as a high frequency filter, the capacitor should be located as close as possible to the SOURCE and PRIMARY BYPASS pins of the device.

The primary sensed OVP function can be realized by connecting a series combination of a Zener diode, a resistor and a blocking diode from the rectified and filtered bias winding voltage supply to the PRIMARY BYPASS pin. The rectified and filtered bias winding output voltage may be higher than expected (up to 1.5x or 2x the desired value) due to poor coupling of the bias winding with the output winding and the resulting ringing on the bias winding voltage waveform. It is therefore recommended that the rectified bias winding voltage be measured. This measurement should be ideally done at the lowest input voltage and with highest load on the output. This measured voltage should be used to select the components required to achieve primary sensed OVP. It is recommended that a Zener diode with a clamping voltage approximately 6 V lower than the bias winding rectified voltage at which OVP is expected to be triggered be selected. A forward voltage drop of 1 V can be assumed for the blocking diode. A small signal standard recovery diode is recommended. The blocking diode prevents any reverse current charging the bias capacitor during start-up. Finally, the value of the series resistor required can be calculated such that a current higher than  $I_{\mbox{\tiny SD}}$  will flow into the PRIMARY BYPASS pin during any output overvoltage.

#### **Reducing No-load Consumption**

The InnoSwitch3-Pro IC can start in self-powered mode from the PRIMARY BYPASS pin capacitor charged through the internal current source. Use of a bias winding is however required to provide supply current to the PRIMARY BYPASS pin once the InnoSwitch3-Pro IC has become operational. Auxiliary or bias winding provided on the transformer is required for this purpose. The addition of a bias winding that provides bias supply to the PRIMARY BYPASS pin enables design of power supplies with no-load power consumption down to <30 mW. Resistor R4 shown in Figure 26 should be adjusted to achieve the lowest no-load input power.

#### Secondary-Side Overvoltage Protection (Auto-Restart Mode)

The secondary-side output overvoltage protection provided by the InnoSwitch3-Pro IC uses an internal auto-restart circuit that is triggered by a threshold current of  $I_{\text{SD}}$  into the SECONDARY BYPASS pin. The direct output sensed OVP function can be realized by connecting a Zener diode from the output to the SECONDARY BYPASS pin. The Zener diode voltage needs to be the difference between the 1.25 times output voltage and 4.4 V SECONDARY BYPASS pin voltage. It is necessary to add a low value resistor, R2 shown in series with the OVP Zener diode to limit the maximum current into SECONDARY BYPASS pin. The secondary-side OVP function is disabled during soft-start.

Under some conditions, the secondary OVP may take several switching cycles to initiate due to the FORWARD pin fall time below ground and timing mismatch between primary and secondary controllers.

## **Selection of Components**

## Components for InnoSwitch3-Pro IC Primary-Side Circuit

#### **BPP Capacitor**

Capacitor connected from the PRIMARY BYPASS pin of the InnoSwitch3-Pro IC provides decoupling for the primary-side controller and also selects current limit. A 0.47  $\mu F$  or 4.7  $\mu F$  capacitor may be used as indicated in InnoSwitch3-Pro IC data sheet. Though electrolytic capacitors can be used, often surface mount multi-layer ceramic capacitors are preferred for use on double sided boards as they enable placement of capacitors close to the IC. Their small size also makes it ideal for design of compact switching power supplies. 16 V or 25 V rated X5R or X7R dielectric capacitors are recommended to ensure minimum capacitance requirements are met.

#### **Bias Winding and External Bias Circuit**

The internal regulator connected from the DRAIN pin of the MOSFET to the PRIMARY BYPASS pin of the InnoSwitch3-Pro IC primary-side controller charges the capacitor connected to the PRIMARY BYPASS pin to achieve start-up. A bias winding should be provided on the transformer with a suitable rectifier and filter capacitor to create a bias supply that can be used to supply at least 1 mA of current to the PRIMARY BYPASS pin.

Turns ratio for the bias winding should be selected such that 7 V is developed across the bias winding at the lowest rated output voltage of the power supply at the lowest (or no-load) load condition. If the voltage is lower than this, the no-load input power will increase. Generally, in USB PD or rapid charge applications, the output voltage range is very wide. For example, a 45 W adapter would need to support 5 V, 9 V and 15 V whereas a 100 W adapter would have output voltages selectable from 5 V to 20 V. Such a wide output voltage variation results in a large change in bias winding output voltage as well. As shown in Figure 26, a linear regulator circuit is generally required to limit the current injected into the PRIMARY BYPASS pin of the InnoSwitch3-Pro IC.

The bias current from the external circuit should be set to approximately 300  $\mu$ A to achieve lowest no-load power consumption when operating the power supply at 230 VAC input voltage, (V<sub>BPP</sub> > 5 V). A glass passivated standard recovery rectifier diode with low junction capacitance is recommended to prevent the snappy recovery typically seen with fast or ultrafast diodes that can lead to higher radiated EMI.

An aluminum capacitor of at least 22  $\mu\text{F}$  with a voltage rating 1.2 times greater than the highest voltage developed across the capacitor is recommended. Highest voltage is typically developed across this capacitor when the supply is operated at the highest rated output voltage and rated load with the lowest input AC supply voltage.

#### **Line UV and OV Protection**

Resistors connected from the UNDER/OVER INPUT VOLTAGE pin to the DC bus enable sensing of input voltage to provide line undervoltage and overvoltage protection. For a typical universal input application, a resistor value of approximately 3.8  $\mbox{M}\Omega$  is recommended. Figure 28 shows circuit configurations that enable selectively either the line UV or the line OV feature, disabling the other.

The InnoSwitch3-Pro IC features a primary sensed OV protection feature that can be used to latch-off the power supply. Once the power supply is latched off, it can be reset if the UNDER/OVER INPUT VOLTAGE pin current is reduced to zero. Once the power supply is latched off, even after input supply is turned off, it can take considerable amount of time to reset InnoSwitch3-Pro IC controller as the energy stored in the DC bus will continue to provide bias supply to the controller. A fast AC reset can be achieved using the modified circuit configuration shown in Figure 29. The voltage across capacitor  $\mathbf{C}_{\mathrm{S}}$  reduces rapidly after input supply is disconnected reducing current into the INPUT VOLTAGE MONITOR pin of the InnoSwitch3-Pro IC and resetting the InnoSwitch3-Pro IC controller.

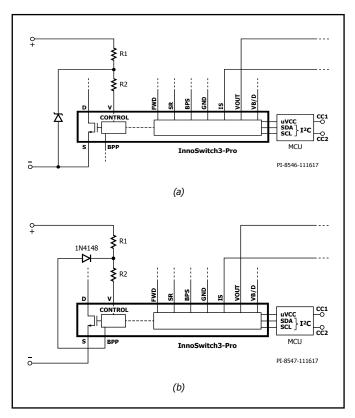


Figure 28. (a) Line OV Only; (b) Line UV Only.

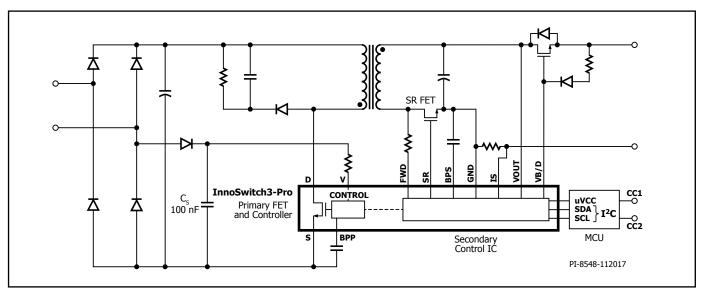


Figure 29. Fast AC Reset Configuration.

#### **Primary Sensed OVP (Overvoltage Protection)**

The voltage developed across the output of the bias winding tracks the power supply output voltage. Though not precise, a reasonably accurate detection of the amplitude of the output voltage can be achieved by the primary-side controller using the bias winding voltage. A Zener diode connected from the bias winding output to the PRIMARY BYPASS pin can reliably detect a secondary overvoltage fault and causes the primary-side controller to latch-off. It is recommended that the highest voltage at the output of the bias winding should be measured for normal steady-state conditions (at full rated load and lowest rated input voltage) and also under transient load conditions. A Zener diode rated for 1.25 times this measured voltage will typically ensure that OVP protection will not trigger under any normal operating conditions but will only operate in case of a fault condition.

## **Primary-Side Snubber Clamp**

A snubber circuit should be used on the primary-side as shown in the example circuit in Figure 26. This prevents excess voltage spikes at the Drain of the MOSFET at the instant of turn-off of the MOSFET during each switching cycle. Though conventional RCD clamps can be used, RCDZ clamps offer the highest efficiency. The circuit example shown in Figure 26 uses RCD clamp with a resistor in series with the clamp diode. This resistor dampens the ringing at the drain and also limits the reverse current through the clamp diode during reverse recovery. Standard recover glass passivated diodes with low junction capacitance are recommended as these enable partial energy recovery from the clamp thereby improving efficiency.

# Components for InnoSwitch3-PRO Secondary-Side Circuit

## SECONDARY BYPASS Pin - Decoupling Capacitor

A 2.2  $\mu$ F, 25 V multi-layer ceramic capacitor should be used for decoupling the SECONDARY BYPASS pin of the InnoSwitch3-Pro IC. Since the SECONDARY BYPASS pin voltage needs to be 4.4 V before the output voltage reaches to the regulation voltage level, a significantly higher BPS capacitor value could lead to output voltage overshoot during start-up. The values lower than 1.5  $\mu$ F may not offer enough capacitance, which can cause unpredictable operation. The capacitor must be located adjacent to the IC pins. The 25 V rating is necessary to guarantee the actual value in operation since the capacitance of ceramic capacitors drops with applied voltage (10 V rated capacitors are not recommended for this reason). Capacitors with X5R or X7R dielectrics should be used for best results.

When the output voltage of the power supply is 5 V or higher, the supply current for the secondary-side controller is supplied by the OUTPUT VOLTAGE (VOUT) pin of the IC as the voltage at this pin is higher than the SECONDARY BYPASS pin voltage. During start-up and operating conditions where the output voltage of the power supply is below 5 V, the secondary-side controller is supplied current from an internal current source connected to the FORWARD pin. If the output voltage of the power supply is below 5 V and the load at the output of the power supply is very light, the operating frequency can drop considerably and the current supplied to the secondary-side controller from the FORWARD pin may not be sufficient to maintain the SECONDARY BYPASS pin voltage at 4.4 V. For such applications, InnoSwitch3-Pro IC has an internal charge pump to regulate the voltage of the SECONDARY BYPASS pin at 4.4 V.

## **FORWARD Pin Resistor**

A 47  $\Omega$  5% resistor is recommended to ensure sufficient IC supply current. A higher or lower resistor value should not be used as it can affect device operation such as the synchronous rectifier drive timing.

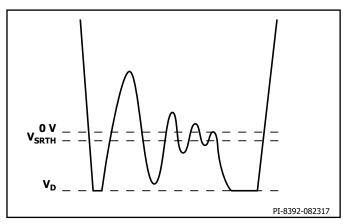


Figure 30. Unacceptable FORWARD Pin Waveform After Handshake With SR FET Conduction During Flyback Cycle.

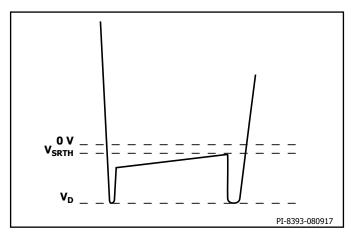


Figure 31. Acceptable FORWARD Pin Waveform After Handshake With SR FET Conduction During Flyback Cycle.

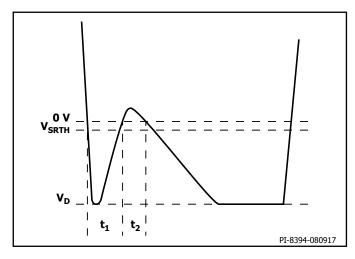


Figure 32. Unacceptable FORWARD Pin Waveform Before Handshake With Body Diode Conduction During Flyback Cycle.

Note:

If  $t_1 + t_2 = 1.5 \ \mu s \pm 50$  ns, the controller may fail the handshake and trigger a primary bias winding OVP latch-off.

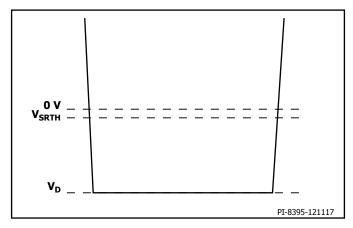


Figure 33. Acceptable FORWARD Pin Waveform Before Handshake With Body Diode Conduction During Flyback Cycle.

#### **SR FET Operation and Selection**

Although a simple diode rectifier and filter works for the output, use of a SR FET enables significant improvement in operating efficiency often necessary to meet the European CoC and the U.S. DoE energy efficiency requirements. The secondary-side controller turns on the SR FET once the flyback cycle begins. The SR FET gate should be tied directly to the SYNCHRONOUS RECTIFIER DRIVE pin of the InnoSwitch3-Pro IC (with no additional resistors connected to the gate circuit of the SR FET if a single SR FET is used). The SR FET is turned off once the Drain voltage of the SR FET drops below 0 V.

A MOSFET with 18 m $\Omega$  R $_{DS(ON)}$  is good for 5 V, 2 A output, and a MOSFET with 8 m $\Omega$  R $_{DS(ON)}$  is suitable for designs rated for 12 V, 3 A output. The SR FET driver uses the SECONDARY BYPASS pin for its supply rail, and this voltage is typically 4.4 V. A MOSFET with too high a threshold voltage is therefore not suitable, and MOSFETs with a low threshold voltage of 1.5 V to 2.5 V are ideal although MOSFETs with a threshold voltage (absolute maximum) as high as 4 V may be used provided their data sheets clearly specify R $_{DS(ON)}$  over-temperature range for a gate voltage of 4.5 V.

There is a slight delay between the commencement of the flyback cycle and the turn-on of the SR FET. During this time, the body diode of the SR FET conducts. If an external parallel Schottky diode is used, this current mostly flows through the Schottky diode. Once the InnoSwitch3-Pro IC detects end of the flyback cycle, voltage across SR FET  $R_{\rm DS(ON)}$  drops below  $V_{\rm SR(TH)'}$  any remaining portion of the flyback cycle is completed with the current commutating to the body diode of the SR FET or the external parallel Schottky diode. A Schottky diode parallel to the SR FET may be added to provide higher efficiency and typically a 1 A surface mount Schottky diode is often adequate. However, the gains are modest; for a 5 V, 2 A design the external diode adds  $\sim\!0.1\%$  to full load efficiency at 85 VAC and  $\sim\!0.2\%$  at 230 VAC.

The voltage rating of the Schottky diode and the SR FET should be at least 1.3 to 1.4 times the expected peak inverse voltage (PIV) based on the turns ratio used for the transformer. 60 V rated MOSFETs and diodes are suitable for most 5 V designs that use a  $V_{\rm OR} < 60$  V, and 100 V rated MOSFETs and diodes are suitable for 12 V design.

## InnoSwitch3-Pro

The interaction between the leakage reactance of the secondary and the SR FET capacitance ( $C_{\rm oss}$ ) leads to ringing on the voltage waveforms at the instance of voltage reversal at the winding due to the primary MOSFET turn-on. This ringing can be suppressed using a RC snubber connected across the SR FET. A snubber resistor in the range of 10  $\Omega$  to 47  $\Omega$  may be used (a higher resistance value leads to noticeable drop in efficiency). A capacitance of 1 nF to 2.2 nF is adequate for most designs.

In designs where the SR FET drain waveform is not as shown in Figure 31 during voltage transitions, and looks similar to Figure 30 it is recommended that voltage transitions be made in small increments of 200 mV.

#### **Output Capacitor**

Low ESR aluminum electrolytic capacitors are suitable for use with most high frequency flyback switching power supplies though the use of aluminum-polymer solid capacitors have gained considerable popularity due to their compact size, stable temperature characteristics, extremely low ESR and high RMS ripple current rating. These capacitors enable design of ultra-compact chargers and adapters.

Typically, 200  $\mu\text{F}$  to 300  $\mu\text{F}$  of aluminum-polymer capacitance per ampere of output current is adequate. The other factor that influences choice of the capacitance is the output ripple. Care should be taken to ensure that capacitors have a voltage rating higher than the highest output voltage with sufficient margin (>20%).

#### **Output Overload Protection**

The maximum power which can be delivered by the power supply is obtained by the product of the programmed  $V_{_{KP}}$  and the full scale current limit. For output voltage below the programmed  $V_{_{KP}}$  threshold, the InnoSwitch3-Pro IC will limit the output current once the programmed current limit is reached (if it is less than the full scale current limit) or voltage across the IS and GND pins exceeds the  $I_{_{\rm SV(TH)}}$  threshold and provides current limited or constant current operation. The full scale current limit is set by the resistor between the IS and GND pins. A lower value of current limit can be programmed over  $I^2C$ . For any output voltage above the programmed  $V_{_{KP}}$  threshold, InnoSwitch3-Pro IC will provide a constant power characteristic. An increase in load current within the programmed current limit will result in a drop in output voltage such that the product of output voltage and current equals the maximum power set by the product of  $V_{_{KP}}$  and set current limit.

#### **Decoupling Capacitor at μVCC Pin**

It is recommended that at least a 2.2  $\mu\text{F}$  ceramic capacitor be placed between the  $\mu\text{VCC}$  and GND pins.

#### **Pull-Up Resistors for SDA and SCL Pins**

A 4.7 k $\Omega$  pull-up resistor from each of the SDA and SCL pin to the  $\mu$ VCC pin is recommended for communication at a frequency of 400 kHz. Maximum value of the pull-up resistor is dependent on the capacitance presented by the SDA/SCL lines and the  $I^2$ C master. The resultant voltage rise to the V $_{\rm IL}$  threshold assuming a total capacitance of 20 pF is tabulated as a function of SCL clock frequency in Table 7.

#### **IS to GND Pin Current Sense Resistor**

This sense resistor is chosen such that the required full scale current produces a 32 mV drop across IS and GND pins. A 1% or lower tolerance resistor is recommended. This sense resistor needs to be placed as close to the InnoSwitch3-Pro IC pins as possible for accurate current measurement and CC regulation.

#### **IS to GND Pin Capacitor**

A 1  $\mu\text{F}$  or higher ceramic capacitor is recommended to be used between the IS and GND pins of the InnoSwitch3-Pro IC for accurate constant current regulation.

#### **Output Decoupling Capacitor**

A ceramic output decoupling capacitor up to 10  $\mu\text{F}$  is required to pass 18 kV ESD air discharge.

#### **Bus Switch**

A low  $R_{\scriptscriptstyle DS(ON)}$  N-MOSFET bus switch is recommended to reduce impact of efficiency at high load currents. The FET need not be a logic level FET. It should be sufficiently enhanced at a gate threshold of 4 V.

#### **Bus Discharge**

The resistor value for bus discharge is chosen as per the discharge time requirements for high-voltage to low-voltage transitions. A  $100~\Omega$  resistor value is recommended to meet the USB PD discharge time specification. A general purpose diode in series is recommended for unidirectional current flow.

#### **External Controller**

An external controller is needed to send the  $I^2C$  commands to the InnoSwitch3-Pro IC over the SDA and SCL lines. For standalone applications, the external controller can get its supply from the  $\mu VCC$  pin of the InnoSwitch3-Pro IC. It should be able to sustain operation for a supply voltage as low as 2.8 V.

## **Recommendations for Circuit Board Layout**

See Figure 34 for a recommended circuit board layout for a switching power supply using InnoSwitch3-Pro IC.

#### Single-Point Grounding

Use a single-point ground connection from the input filter capacitor to the area of copper connected to the SOURCE pins.

#### **Bypass Capacitors**

The PRIMARY BYPASS and SECONDARY BYPASS pin capacitor must be located directly adjacent to the PRIMARY BYPASS-SOURCE and SECONDARY BYPASS-SECONDARY GROUND pins respectively and connections to these capacitors should be routed with short traces.

#### **Primary Loop Area**

The area of the primary loop that connects the input filter capacitor, transformer primary and IC should be kept as small as possible.

#### **Primary Clamp Circuit**

A clamp is used to limit peak voltage on the DRAIN pin at turn-off. This can be achieved by using an RCD clamp or a Zener diode (~200 V) and diode clamp across the primary winding. To reduce EMI, minimize the loop from the clamp components to the transformer and IC.

#### **Thermal Considerations**

The SOURCE pin is internally connected to the IC lead frame and provides the main path to remove heat from the device. Therefore the SOURCE pin should be connected to a copper area underneath the IC to act not only as a single point ground, but also as a heat sink. As this area is connected to the quiet source node, this area should be maximized for good heat sinking. Similarly for output SR MOSFET, maximize the PCB area connected to the pins on the package through which heat is dissipated from the SR MOSFET.

Sufficient copper area should be provided on the board to keep the IC temperature safely below the absolute maximum limits. It is recommended that the copper area provided for the copper plane on which the SOURCE pin of the IC is soldered is sufficiently large to keep the IC temperature below 85 °C when operating the power supply at full rated load and at the lowest rated input AC supply voltage. Further de-rating can be applied depending on any additional specific requirements.

#### Y Capacitor

The Y capacitor should be placed directly between the primary input filter capacitor positive terminal and the output positive or return terminal of the transformer secondary. Such a placement will route high amplitude common mode surge currents away from the IC. Note – if an input  $\pi$  (C, L, C) EMI filter is used then the inductor in the filter should be placed between the negative terminals of the input filter capacitors.

#### **Output SR FET**

For best performance, the area of the loop connecting the secondary winding, the output SR FET and the output filter capacitor, should be minimized. In addition, sufficient copper area should be provided at the terminals of the SR FET for heat sinking.

#### **ESD**

Sufficient clearance should be maintained (>8 mm) between the primary-side and secondary-side circuits to enable easy compliance with any ESD / hi-pot requirements.

The spark gap is best placed directly between output positive rail and one of the AC inputs. In this configuration a 6.4 mm spark gap is often sufficient to meet the creepage and clearance requirements of

many applicable safety standards. This is less than the primary to secondary spacing because the voltage across spark gap does not exceed the peak of the AC input.

#### **Drain Node**

The drain switching node is the dominant noise generator. As such the components connected the drain node should be placed close to the IC and away from sensitive feedback circuits. The clamp circuit components should be located physically away from the PRIMARY BYPASS pin and associated circuit trace lengths should be minimized.

The loop area of the loop comprising of the input rectifier filter capacitor, the primary winding and the IC primary-side MOSFET should be kept as small as possible.

## **Layout Example**

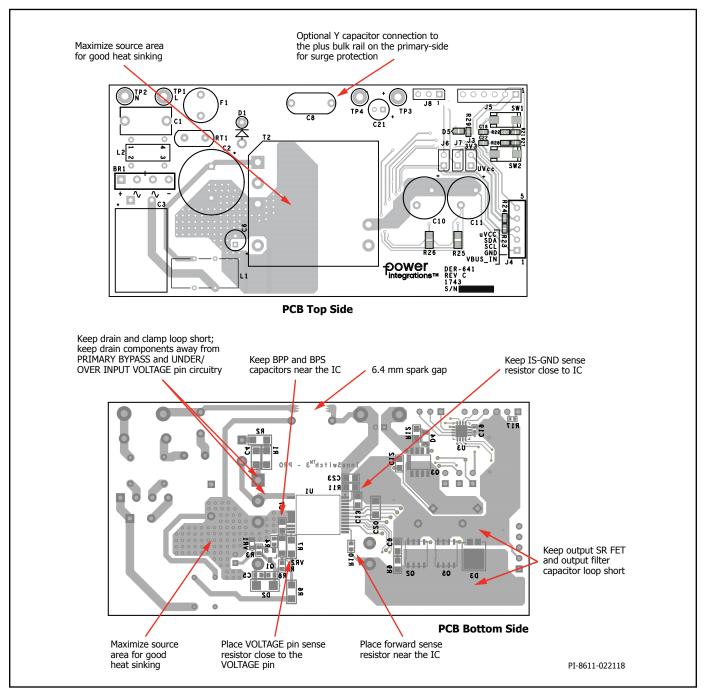


Figure 34. PCB for DER-641.

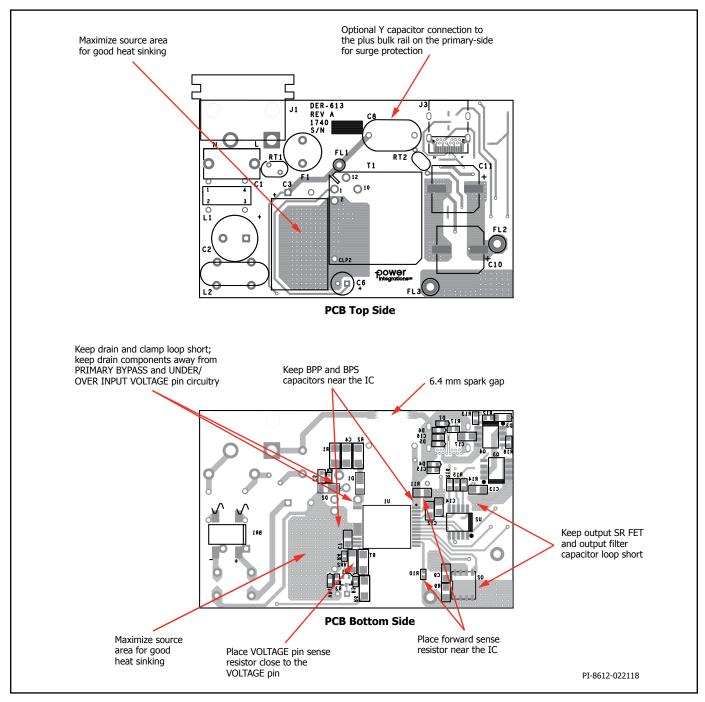


Figure 35. PCB for DER-613.

## **Recommendations for EMI Reduction**

- Appropriate component placement and small loop areas of the primary and secondary power circuits help minimize radiated and conducted EMI. Care should be taken to achieve a compact loop area.
- A small capacitor in parallel to the clamp diode on the primaryside can help reduced radiated EMI.
- 3. A resistor in series with the bias winding helps reduce radiated EMI.
- Common mode chokes are typically required at the input of the power supply to sufficiently attenuate common mode noise. The same can be achieved by using shield windings on the transformer.
- Shield windings can also be used in conjunction with common mode filter inductors at input to achieve improved conducted and radiated EMI margins.
- Values of components of the RC snubber connected across the output SR FET can help reduce high frequency radiated and conducted EMI.
- 6. A  $\pi$  filter comprising of differential inductors and capacitors can be used in the input rectifier circuit to reduce low frequency differential EMI.
- 7. A 1  $\mu F$  or higher ceramic capacitor when connected at the output of the power supply helps to reduce radiated EMI.

## **Recommendations for Transformer Design**

Transformer design must ensure that the power supply is able to deliver the rated power at the lowest input voltage. The lowest voltage on the rectified DC bus of the power supply depends on the capacitance of the filter capacitor used. At least 2  $\mu\text{F}$  / W is recommended to keep the DC bus voltage always above 70 V, though 3  $\mu\text{F}$  / W provides sufficient margin. The ripple on the DC bus should be measured and care should be taken to verify this voltage to confirm the design calculations for transformer primary-winding inductance selection.

#### Switching Frequency (F<sub>sw</sub>)

It is a unique feature in InnoSwitch3-Pro ICs that a designer can set the switching frequency at full load between 25 kHz to 95 kHz depending on the design specification. To have lower device temperature, the switching frequency can be set to around 60 kHz. To have smaller size transformer, the switching frequency needs to be set to a value closer to a maximum of 95 kHz. When setting the full load switching frequency, it is important to consider primary inductance and peak current tolerances to ensure that average switching frequency does not exceed 110 kHz which may trigger auto-restart due to overload protection. The following table provides a guide for frequency selection based on the device size. This represents the best compromise between the overall device losses (conduction and switching losses) based on size of the internal high-voltage MOSFET.

INN3365C/3375C	80 kHz
INN3366C/3376C	75 kHz
INN3377C	70 kHz
INN3367C/3368C	65 kHz

## Reflected Output Voltage, $V_{OR}$ (V)

This parameter describes the effect on the primary MOSFET Drain voltage of the secondary-winding voltage during the diode / SR conduction which is reflected back to the primary through the turns ratio of the transformer. To make full use of QR capability and ensure flattest efficiency over line / load, it is better to set reflected output voltage ( $V_{\text{OR}}$ ) to maintain  $K_{\text{p}}=0.8$  at minimum input voltage conditions for universal line input and  $K_{\text{p}}=1$  for high-line input only conditions.

The following should be kept in mind for design optimization:

- Higher V<sub>OR</sub> allows increased power delivery at V<sub>MIN</sub>, which minimizes the value of the input capacitor and maximizes power delivery from a given InnoSwitch3-Pro device.
- 2. Higher  $V_{\rm OR}$  reduces the voltage stress on the output diodes and SR MOSFETs.
- 3. Higher  $V_{OR}$  increases leakage inductance that reduces efficiency of the power supply.
- 4. Higher  $V_{\rm OR}$  increases peak and RMS current on the secondary-side which may increase secondary-side copper and diode losses.

There are some exceptions to this. For very high output currents where the  $\rm V_{\rm OR}$  should be reduced to get highest efficiency, and higher output voltages above 15 V,  $\rm V_{\rm OR}$  should be higher to maintain a reasonable PIV across the output synchronous rectifier.

#### Ripple to Peak Current Ratio, K.

A  $K_p$  below 1, indicates continuous conduction mode,  $K_p$  is the ratio of ripple-current to peak-primary-current (Figure 37).

$$K_p \equiv K_{pp} = I_p / I_p$$

A value of  $K_{\rm p}$  higher than 1, indicates discontinuous conduction mode. In this case,  $K_{\rm p}$  is the ratio of primary MOSFET off-time to the secondary diode conduction-time.

$$K_{\scriptscriptstyle P} \equiv K_{\scriptscriptstyle DP} = (1-D)\,x\,T\,/\,t = V_{\scriptscriptstyle OR} \times (1-D_{\scriptscriptstyle MAX})\,/\,(V_{\scriptscriptstyle MIN} - V_{\scriptscriptstyle DS}) \times D_{\scriptscriptstyle MAX}$$

It is recommended that a  $K_{\rm p}$  close to 0.9 at the minimum expected DC bus voltage should be used for most InnoSwitch3-Pro IC designs. A  $K_{\rm p}$  value of <1 results in higher transformer efficiency by lowering the primary RMS current but results in higher switching losses in the primary-side MOSFET resulting in higher InnoSwitch3-Pro IC temperature. The benefits of quasi-resonant switching start to diminish for a further reduction in  $K_{\rm p}$ .

For typical USB PD and rapid charge designs which require a wide output voltage range,  $K_{\rm p}$  will change significantly as the output voltage changes.  $K_{\rm p}$  will be high for high output voltage conditions and will drop as the output voltage is lowered. PIXIs spreadsheet from Power Integrations can be used to effectively optimize selection of  $K_{\rm p}$  inductance of the primary winding, turns ratio of the transformer and the operating frequency while ensuring appropriate design margins.

## **Core Type**

Choice of suitable core is dependent on the physical design constraints of the power supply enclosure. It is recommended that only cores with low loss be used as power supply designs are often thermally challenged due to the small enclosure requirement.

#### Safety Margin, M (mm)

For designs that require safety isolation between primary and secondary but are not using triple insulated wire, the width of the safety margin to be used on each side of the bobbin is important. For universal input designs, a total margin of 6.2 mm is typically required, and a value of 3.1 mm being used on either side of the winding. For vertical bobbins the margin may not be symmetrical. However if a total margin of 6.2 mm is required then the physical margin can be placed only on one side of the bobbin. For designs using triple insulated wire it may still be necessary to use a small margin in order to meet the required safety creepage distances. Many bobbins exist for each core size and each will have different mechanical spacing. Refer to the bobbin data sheet or seek guidance from your safety expert or transformer vendor to determine what specific margin is required. As the margin reduces the available area for the windings, margin construction may not be suitable for small core sizes. It is recommended that for compact power supply designs using an InnoSwitch3-Pro IC, triple insulated wire should be used for secondary which then eliminates need for margins.

#### **Primary Layers, L**

Primary layers should be in the range of 1 < L < 3 and in general it should be the lowest number that meets the primary current density limit (CMA). A value of  $\geq 200$  Cmils / Amp can be used as a starting point for most designs though higher values may be required based on thermal design constraints. Designs with more than 3 layers are possible but the increased leakage inductance and physical fit of the windings should be considered. A split primary construction may be helpful for designs where clamp dissipation due to leakage inductance

is too high. In split primary construction, half of the primary winding is placed on either side of the secondary (and bias) winding in a sandwich arrangement. This arrangement is often disadvantageous for low power designs as this typically increases common mode noise and adds cost to the input filtering.

## Maximum Operating Flux Density, B<sub>M</sub> (Gauss)

A maximum value of 3800 gauss at the peak device current limit (at 132 kHz) is recommended to limit the peak flux density under start-up and under output short-circuit conditions. Under these conditions the output voltage is low and little reset of the transformer occurs during the MOSFET off-time. This allows the transformer flux density to staircase beyond the normal operating level. A value of 3800 gauss at the peak current limit of the selected device together with the built-in protection features of InnoSwitch3-Pro IC provides sufficient margin to prevent core saturation under start-up or output short-circuit conditions.

#### **Transformer Primary Inductance, (LP)**

Once the lowest operating input voltage, switching frequency at full load, and the required  $V_{\rm OR}$  are determined, transformer primary inductance can be calculated. The PIXIs design spreadsheet which is part of the free PI Expert suite can be used to assist in designing the transformer.

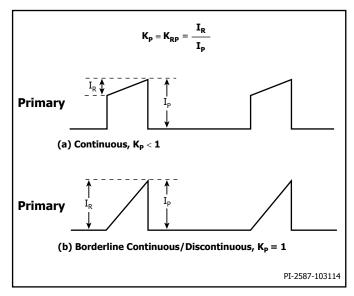


Figure 37. Continuous Mode Current Waveform,  $K_p \leq 1$ .

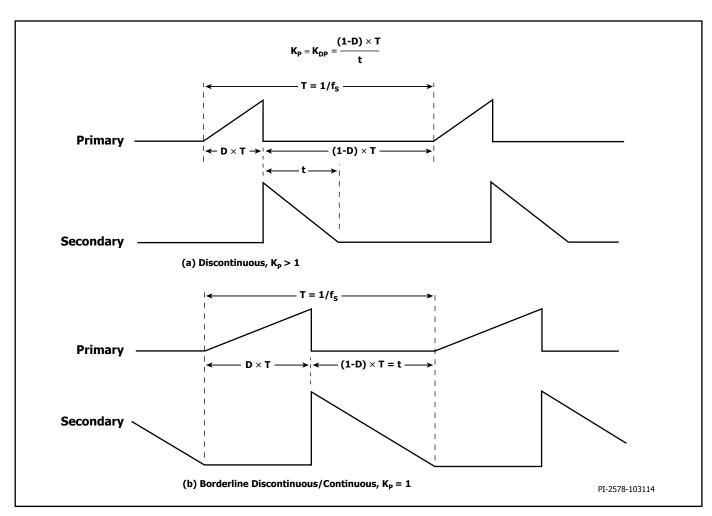


Figure 36. Discontinuous Mode Current Waveform,  $K_p \ge 1$ .

## InnoSwitch3-Pro

## **Quick Design Checklist**

As with any power supply design, all InnoSwitch3-Pro designs should be verified on the bench to make sure that component limits are not exceeded under worst-case conditions.

The following minimum set of tests is strongly recommended:

- Maximum Drain Voltage Verify that V<sub>DS</sub> of InnoSwitch3-Pro and SR MOSFET do not exceed 90% of breakdown voltages at highest input voltage and peak (overload) output power in normal operating and start-up conditions.
- Maximum Drain Current At maximum ambient temperature, maximum input voltage and peak output (overload) power, verify drain current waveforms for any signs of transformer saturation and excessive leading edge current spikes at start-up. Repeat

under steady-state conditions and verify that the leading edge current spike event is below  $I_{\text{LIMIT}(\text{MIN})}$  at the end of the  $t_{\text{LEB}(\text{MIN})}.$  Under all conditions, the maximum drain current should be below the specified absolute maximum ratings.

Thermal Check – At specified maximum output power, minimum input voltage and maximum ambient temperature, verify that the temperature specification limits are not exceeded for InnoSwitch3-Pro IC, transformer, output SR MOSFET, and output capacitors. Enough thermal margin should be allowed for part-to-part variation of the  $R_{\text{DS(ON)}}$  of InnoSwitch3-Pro IC as specified in the data sheet.

Under low-line, maximum power, a maximum InnoSwitch3-Pro IC SOURCE pin temperature of 110  $^{\circ}\text{C}$  is recommended to allow for these variations.

# Absolute Maximum Ratings1,2

INN33x7C	
	2.96 A (5.55 A) <sup>3</sup>
BPP/BPS Pin Voltage	
BPP/BPS Current	100 mA
SCL, SDA, uVCC Pin Voltage	0.3 to 6 V
uVCC Current <sup>6</sup>	
FWD Pin Voltage	1.5 V to 150 V
SR Pin Voltage	0.3 V to 6 V
V Pin Voltage (INN336x)	
V Pin Voltage (INN337x)	0.3 V to 725 V
VOUT Pin Voltage	0.3 V to 27 V
Storage Temperature	
Operating Junction Temperature <sup>4</sup>	

Ambient Temperature40 to	o 105 °C
Lead Temperature <sup>5</sup>	.260 °C

#### Notes:

- 1. All voltages referenced to SOURCE and Secondary GROUND,  $\rm T_{\rm A} = 25~^{\circ}C.$
- Maximum ratings specified may be applied one at a time without causing permanent damage to the product. Exposure to Absolute Maximum Ratings conditions for extended periods of time may affect product reliability.
- 3. Higher peak Drain current is allowed while the Drain voltage is simultaneously less than 400 V.
- 4. Normally limited by internal circuitry.
- 5. 1/16" from case for 5 seconds.
- 6. Only at 5 V output, the uVCC pin can supply 50 mA maximum current for 0.5 seconds.

# **Thermal Resistance**

Thermal Resistance:

# Notes:

- 1. Soldered to 0.36 sq. inch (232 mm $^2$ ) 2 oz. (610 g/m $^2$ ) copper clad.
- 2. Soldered to 1 sq. inch (645 mm<sup>2</sup>), 2 oz. (610 g/m<sup>2</sup>) copper clad.
- 3. The case temperature is measured on the top of the package.

Parameter	Conditions	Rating	Units
Ratings for UL1577			
Primary-Side Current Rating	Current from pin (16-19) to pin 24	1.5	A
Primary-Side Power Rating	$T_{AMB} = 25  ^{\circ}\text{C}$ (device mounted in socket resulting in $T_{CASE} = 120  ^{\circ}\text{C}$ )	1.35	W
Secondary-Side Power Rating	T <sub>AMB</sub> = 25 °C (device mounted in socket)	0.125	W

Parameter	Conditions	Rating	Units
Package Characteristics			
Clearance		12.1	mm (typ)
Creepage		11.7	mm (typ)
Distance Through Insulation (DTI)		0.4	mm (min)
Transient Isolation Voltage		6	kV (min)
Comparative Tracking Index (CTI)		600	-

Parameter	Symbol	Condition  SOURCE = 0 $T_{_{J}}$ = -40 °C to 1  (Unless Otherwise	Min	Тур	Max	Units	
<b>Control Functions</b>							
Startup Switching Frequency	f <sub>sw</sub>	T <sub>1</sub> = 25 °C		23	25	27	kHz
Jitter Modulation Frequency	f <sub>M</sub>	T <sub>J</sub> = 25 °C f <sub>SW</sub> = 100 kH	lz	0.80	1.25	1.70	kHz
Maximum On-Time	t <sub>ON(MAX)</sub>	T <sub>3</sub> = 25 °C		12.4	14.6	16.9	μS
Minimum Primary Feedback Block-Out Timer	t <sub>BLOCK</sub>					t <sub>OFF(MIN)</sub>	μS
	$I_{s_1}$	$V_{BPP} = V_{BPP} + 0$ (MOSFET not Swith $T_{_{\mathrm{J}}} = 25~{}^{\circ}\mathrm{C}$	.1 V tching)	145	200	425	μΑ
			INN3365C	0.49	0.65	1.03	
			INN3366C	0.64	0.86	1.21	mA
BPP Supply Current		$V_{BPP} = V_{BPP} + 0.1 V$	INN3367C	0.77	1.03	1.38	
	I <sub>S2</sub>	(MOSFET Switching at 132 kHz) T <sub>3</sub> = 25 °C	INN3368C	0.90	1.20	1.75	
			INN3375C	0.59	0.79	1.10	
			INN3376C	0.77	1.02	1.38	
			INN3377C	0.90	1.20	1.73	
DDD Din Chaves Current	I <sub>CH1</sub>	$V_{BP} = 0 \text{ V, } T_{J} = 2$	25 °C	-1.73	-1.35	-0.88	m A
BPP Pin Charge Current	I <sub>CH2</sub>	$V_{BP} = 4 \text{ V, } T_{J} = 2$	25 °C	-5.98	-4.65	-3.32	— mA
BPP Pin Voltage	V <sub>BPP</sub>	T <sub>3</sub> = 25 °C		4.65	4.90	5.15	V
BPP Pin Voltage Hysteresis	V <sub>BPP(H)</sub>			0.22	0.39	0.55	V
BPP Shunt Voltage	V <sub>SHUNT</sub>	$I_{BPP} = 2 \text{ mA}$		5.15	5.36	5.65	V
BPP Power-Up Reset Threshold Voltage	V <sub>BPP(RESET)</sub>	T <sub>3</sub> = 25 °C		2.80	3.15	3.60	V
UV/OV Pin Brown-In Threshold	I <sub>UV+</sub>	T <sub>3</sub> = 25 °C		23.95	26.06	28.18	μА
UV/OV Pin Brown-Out Threshold	I <sub>UV-</sub>	T <sub>3</sub> = 25 °C		21.96	23.72	25.47	μА
Brown-Out Delay Time	t <sub>uv-</sub>				32		ms
UV/OV Pin Line Overvoltage Threshold	I <sub>OV-</sub>	T <sub>3</sub> = 25 °C		106	115	118	μА
UV/OV Pin Line Overvoltage Hysteresis	I <sub>OV(H)</sub>	T <sub>3</sub> = 25 °C		6	7	8	μА

Parameter	Symbol	Condit SOURCE $T_{J} = -40$ °C (Unless Otherw	Min	Тур	Max	Units	
Line Fault Protection	,			,	1	1	
VOLTAGE Pin Line Over- voltage Deglitch Filter	t <sub>ov+</sub>	$T_{j} = 2$	5 ℃		3		μS
VOLTAGE Pin Voltage Rating	V <sub>v</sub>	T <sub>1</sub> = 25 °C See Note B	INN336x INN337x	650 725			V
Circuit Protection						1	
		di/dt = 212.5 mA/ $\mu$ s T $_{_{\mathrm{J}}}$ = 25 °C	INN33x5C	883	950	1017	
Standard Current Limit (BPP) Capacitor =		di/dt = 237.5 mA/ $\mu$ s T $_{_{\rm J}}$ = 25 °C	INN33x6C	1162	1250	1338	
Ò.47 μF	I <sub>LIMIT</sub>	di/dt = 300 mA/μs	INN3377C	1255	1350	1445	mA
See Note D	$T_{3} = 25  ^{\circ}\text{C}$ $di/dt = 375  \text{mA}/\mu \text{s}$ $T_{3} = 25  ^{\circ}\text{C}$		INN3367C	1348	1450	1552	
		INN3368C	1534	1650	1766		
		di/dt = 212.5 mA/ $\mu$ s T $_{_{\mathrm{J}}}$ = 25 °C	INN33x5C	1046	1150	1254	
Increased Current Limit			di/dt = 237.5 mA/ $\mu$ s T <sub>1</sub> = 25 °C	INN33x6C	1319	1450	1581
(BPP) Capacitor = 4.7 μF	$I_{LIMIT+1}$	di/dt = 300 mA/μs	INN3377C	1410	1550	1689	mA
See Note D		T <sub>1</sub> = 25 °C	INN3367C	1501	1650	1799	
		di/dt = 375 mA/ $\mu$ s T $_{_{\mathrm{J}}}$ = 25 °C	INN3368C	1683	1850	2017	
Overload Detection Frequency	f <sub>ovL</sub>	$T_{j} = 2$	5 ℃	102	110	118	kHz
BYPASS Pin Latching/ Auto-Restart Shutdown Threshold Current	$I_{_{\mathrm{SD}}}$	T <sub>3</sub> = 25 °C		6.0	8.9	11.3	mA
Auto-Restart On-Time	t <sub>AR</sub>	T <sub>1</sub> = 25 °C		75	82	89	ms
Auto-Restart Trigger Skip Time	t <sub>ar(sk)</sub>	T <sub>J</sub> = 25 °C See Note A			1.3		sec
Auto-Restart Off-Time	t <sub>AR(OFF)</sub>	$T_{J} = 2$	5 °C	1.7		2.11	sec
Short Auto-Restart Off-Time	t <sub>AR(OFF)SH</sub>	T <sub>1</sub> = 2	 5 ℃	0.17	0.20	0.23	sec



Parameter	Symbol	Cond SOURC $T_{J} = -40  ^{\circ}\text{C}$ (Unless Other	Min	Тур	Max	Units	
Output							
		INN3365C	T <sub>1</sub> = 25 °C		1.95	2.24	
		$I_{D} = I_{LIMIT+1}$	T <sub>J</sub> = 100 °C		3.02	3.47	
		INN3375C	T <sub>1</sub> = 25 °C		1.95	2.24	
		$I_{_{D}} = I_{_{LIMIT+1}}$	T <sub>J</sub> = 100 °C		3.02	3.47	
		INN3366C	T <sub>1</sub> = 25 °C		1.30	1.50	
		$I_{D} = I_{LIMIT+1}$	T <sub>1</sub> = 100 °C		2.02	2.32	
ON Chata Basistana		INN3376C	T <sub>1</sub> = 25 °C		1.34	1.54	
ON-State Resistance	R <sub>DS(ON)</sub>	$I_{D} = I_{LIMIT+1}$	T <sub>3</sub> = 100 °C		2.08	2.39	Ω
		$INN3367C$ $I_{D} = I_{LIMIT+1}$	T <sub>1</sub> = 25 °C		1.02	1.17	
			T <sub>J</sub> = 100 °C		1.58	1.82	
		$\begin{array}{c} \text{INN3377C} \\ \text{I}_{\text{D}} = \text{I}_{\text{LIMIT+1}} \end{array}$	T <sub>3</sub> = 25 °C		1.20	1.38	
			T <sub>1</sub> = 100 °C		1.86	2.14	
		$INN3368C$ $I_{D} = I_{LIMIT+1}$	T <sub>3</sub> = 25 °C		0.86	0.99	
			T <sub>1</sub> = 100 °C		1.33	1.53	
OFF-State Drain	$I_{ extsf{DSS1}}$	$V_{BPP} = V_{BI}$ $V_{DS} = T_{J} = 0$	<sub>Dpp</sub> + 0.1 V 150 V 25 °C		15		μА
Leakage Current	$I_{ extsf{DSS2}}$	$V_{BPP} = V_{BPP} + 0.1 \text{ V}$ $V_{DS} = 325 \text{ V}$ $T_{J} = 25 \text{ °C}$				200	μА
Decaded and M. P.	D) /	$V_{ppp} = V_{ppp} + 0.1 \text{ V}$	INN336xC	650			V
Breakdown Voltage	BV <sub>DSS</sub>	$V_{BPP} = V_{BPP} + 0.1 V$ $T_{J} = 25 \text{ °C}$	INN337xC	725			
Drain Supply Voltage				50			V
Thermal Shutdown	T <sub>SD</sub>	See N	lote A	135	142	150	°C
Thermal Shutdown Hysteresis	T <sub>SD(H)</sub>	See N	lote A		70		°C

Parameter	Symbol	Conditions  SOURCE = 0 V $T_3 = -40$ °C to 125 °C  (Unless Otherwise Specified)	Min	Тур	Max	Units
Secondary						
Maximum Secondary Frequency	$f_{SREQ}$	T <sub>1</sub> = 25 °C	118	132	145	kHz
Minimum Off-time	t <sub>off(MIN)</sub>		2.48	3.38	4.37	μS
BPS Pin Latch Command Shutdown Threshold Current	I <sub>BPS(SD)</sub>		5.2	8.9	12	mA
Start-up VOUT Pin Regulation Voltage	VOUT <sub>REG</sub>	T <sub>J</sub> = 25 °C	4.9	5	5.1	V
Outrust Voltage	$V_{OUT(R)}$	Default = 5 V	3.00		24.00	V
Output Voltage Programming Range	TOL <sub>VOUT</sub>	Tolerance T <sub>J</sub> = 25 °C	-3		+3	%
Output Voltage Step Size	$\Delta V_{ m OUT}$	T <sub>J</sub> = 25 °C		10		mV
Report-Back Output Voltage Tolerance	V <sub>OUT(T)</sub>	T <sub>3</sub> = 25 °C	-3		+3	%
Normalized Output	T	0.6 - 1.0 T <sub>1</sub> = 25 °C, See Note C	-5		+5	%
Current	I <sub>OUT</sub>	$0.2$ $T_{_{\rm J}}$ = 25 °C, See Note C	-15		+15	70
Normalized Output Current Step Size	$\Delta \mathbf{I}_{OUT}$	T <sub>J</sub> = 25 °C		0.78		%
Maximum V/I Update Rate	t <sub>vi</sub>	See Note B		10		ms
Minimum Time Delay Between I <sup>2</sup> C Commands	t <sub>delay</sub>	See Note B	150			μS
Internal Current Limit Voltage Threshold	$I_{\text{SV(TH)}}$	$T_{\rm J}$ = 25 °C Across External IS to GND Pin Resistor		32		mV
Cable Drop Compensa- tion (CDC) Programming Range	$\Delta \phi_{CD}$	$T_{j} = 25 \text{ °C}$ Default = 0 V	0		600	mV
CDC Tolerance	TOLφ <sub>CD</sub>	$CDC \ge 100 \text{ mV}$ $T_{\text{J}} = 25 \text{ °C}$	-25		25	mV
CDC Programming Step Size	$\Delta \phi_{CD}$			50		mV
Output Overvoltage Programming Range	V <sub>OVA</sub>	Default = 6.2 V	6.2		25	V
Output Overvoltage Tolerance	TOL <sub>OVA</sub>	T <sub>1</sub> = 25 °C	-3		3	%
Output Overvoltage Programming Step Size	$\Delta V_{\scriptscriptstyle  m OVA}$			100		mV
Output Undervoltage Programming Range	V <sub>UVA</sub>	Default = 3.6 V	3		24	V
Output Undervoltage Tolerance	TOL <sub>UVA</sub>	T <sub>J</sub> = 25 °C	-3		3	%



Parameter	Symbol	Conditions  SOURCE = 0 V $T_{J} = -40$ °C to 125 °C  (Unless Otherwise Specified)		Min	Тур	Max	Units
Secondary (cont.)							
Output Undervoltage Programming Step Size	$\Delta V_{_{ m UVA}}$				100		mV
			Programming Option 1		8		
Output Undervoltage		T 25.00	Programming Option 2		16		
Timer Programming Options	t <sub>uvL</sub>	T <sub>1</sub> = 25 °C See Notes B, E	Programming Option 3		32		ms
options -			Default Programming Option 4		64		
Constant Output Power Onset Threshold Programming Range	V <sub>PK</sub>	D	pefault = 24 V	5.3		24	V
Constant Output Power Tolerance	TOLP <sub>OUT</sub>	At F	ull Scale Current	-10		+10	%
Constant Output Power Onset Threshold Programming Step Size	$\Delta V_{PK}$				100		mV
Constant Voltage Mode			Programming Option 1		8		
		T <sub>3</sub> = 25 °C See Notes B, E	Programming Option 2		16		ms
Timer Programming Options	See Notes I		Programming Option 3		32		
			Programming Option 4		64		
		Default P	rogramming Option 1 See Note B		0.5		
Watchdog Timer	t <sub>wdt</sub>	Programming Option 2, See Note B			1		sec
		Programming Option 3, See Note B			2		
VB/D Drive Voltage	V <sub>VB/D</sub>	With Re	espect to VOUT Pin	4		10	V
VB/D Turn-On Time	t <sub>R(VB/D)</sub>	(	$T_{\rm J} = 25$ °C $C_{\rm LOAD} = 10$ nF		4	10	ms
VB/D Turn-Off Time	t <sub>F(VB/D)</sub>	(	$T_{\rm J}$ = 25 °C $C_{\rm LOAD}$ = 10 nF		4	10	μS
VB/D Pin Load Dis- charge Internal MOSFET On-State Resistance	R <sub>B/D(ON)</sub>			20	35	70	Ω
VB/D Pin Load Dis- charge Internal MOSFET Off-State Resistance	R <sub>B/D(OFF)</sub>			80			kΩ
Secondary Over-	_		amming Option 1 See Note B		40		20
Temperature Hysteresis	T <sub>SEC(HYS)</sub>	Progr	ramming Option 2 See Note B		60		- °C
VOUT Pin Bleeder Current	IVO <sub>BLD</sub>		VOUT = 5 V	170	270	370	mA

Parameter	Symbol	Conditions  SOURCE = 0 V $T_{j} = -40$ °C to 125 °C  (Unless Otherwise Specified)		Min	Тур	Max	Units
Secondary (cont.)	<u>'</u>						'
uVCC Supply Voltage	uVCC	$oldsymbol{\mathrm{I}}_{ ext{uVCC}}: oldsymbol{\mathrm{V}}_{ ext{OUT}}:$	= 0 A = 5 V	3.42	3.60	3.78	V
Maximum aVCC Summly		$uVCC > 3.3 Y$ $T_{j} = 3$	v, v <sub>out</sub> = 5 v 25 °C	50			
Maximum uVCC Supply Current	I <sub>uvcc</sub>	uVCC > 3.9 V T <sub>J</sub> = 2	≤ V <sub>OUT</sub>	10			mA
uVCC Pin Output Resistance	R <sub>uvcc</sub>	$T_{j} = 3$	25 °C	18	21	24	Ω
uVCC Reset Voltage Threshold	uVCC <sub>RST</sub>	See N	lote B			2.65	V
BPS Pin Voltage	V <sub>BPS</sub>			4.2	4.4	4.6	V
BPS Pin Current	I <sub>SNL</sub>	T <sub>J</sub> = 2 VBUS Swi			0.67	0.85	- mA
DF3 Fill Current	*SNL	$T_{_{\mathrm{J}}} = 2$ VBUS Swit	25 °C cch Closed		1.03	1.3	IIIA
BPS Pin Undervoltage Threshold	V <sub>BPS(UVLO)TH</sub>			3.6	3.8	4.0	V
BPS Pin Undervoltage Hysteresis	V <sub>BPS(UVLO)TH</sub>				0.65		V
Soft Start Frequency Ramp Time	t <sub>SS(RAMP)</sub>	$T_{j} = 3$	25 °C	7.5	11.75	16	ms
FORWARD Pin Breakdown Voltage	BV <sub>FWD</sub>			150			V
Synchronous Rectifier @	T <sub>1</sub> = 25 °C				l	l	ı
SR Pin Drive Voltage	V <sub>SR</sub>			4.2	4.4	4.6	V
SR Pin Voltage Threshold	V <sub>SR(TH)</sub>				-2.5	0	mV
SR Pin Pull-Up Current	I <sub>SR(PU)</sub>	$T_{\rm J} = 2$ $C_{\rm LOAD} = 2 \text{ nF,}$	25 °C f <sub>s</sub> = 100 kHz	135	165	195	mA
SR Pin Pull-Down Current	I <sub>SR(PD)</sub>	$T_{J} = 2$ $C_{LOAD} = 2 \text{ nF,}$	25 °C f <sub>s</sub> = 100 kHz	87	97	107	mA
Rise Time	t <sub>R(SR)</sub>	$T_{_{\mathrm{J}}} = 25  ^{\circ}\mathrm{C}$ $C_{_{\mathrm{LOAD}}} = 2\mathrm{nF}$	0-100%		71		ns
	,,,,	See Note B	10-90%		40		
Fall Time	t <sub>F(SR)</sub>	T <sub>J</sub> = 25 °C 0-100% C <sub>LOAD</sub> = 2nF See Note B 10-90%			32 15		ns
Output Pull-Up Resistance	R <sub>pU</sub>	$T_{\rm J} = 25~{\rm °C}$ $V_{\rm BPS} + 0.1~{\rm V}$ $I_{\rm SR} = 30~{\rm mA}$		7.5	8.9	10.5	Ω
Output Pull-Down Resistance	R <sub>PD</sub>	$ T_{J} = 2 $ $ V_{BPS} + 1 $ $ I_{SR} = 3 $	0.2 V	10.7	12.7	15	Ω



Parameter	Symbol	Conditions  SOURCE = 0 V $T_{j} = -40$ °C to 125 °C  (Unless Otherwise Specified)	Min	Тур	Max	Units
I <sup>2</sup> C Bus Specifications (SI	OA and SCL Pi	ins) *See Note B	'			
SCL Clock Frequency	$f_{_{SCL}}$		50	400	700	kHz
Low-level Input Voltage	$V_{_{\rm IL}}$		-0.5		0.3 × uVCC	٧
High-level Input Voltage	$V_{_{\mathrm{IH}}}$		0.7 × uVCC		uVCC + 0.5 V	٧
Hysteresis of Schmitt Trigger Inputs	$V_{HYS}$		0.05 × uVCC			V
Low-Level Output Voltage (Open Drain or Collector)	V <sub>OL</sub>	uVCC >2.8 V 3 mA Sink Current	0		0.4	V
Low-level Output Current	$\mathbf{I}_{OL}$		3			mA
Output Fall-Time from $V_{\rm IH(MIN)}$ to $V_{\rm IL(MAX)}$	t <sub>of</sub>	Bus Capacitance from 10 pF to 400 pF	-		250	ns
SDA/SCL Input Current	$\mathbf{I}_{_{\mathrm{I}}}$	$(0.1 \times \text{uVCC}) < (\text{V}_{\text{SCL}}/\text{V}_{\text{SDA}}) < (0.9 \times \text{uVCC})$	-1		1	μА
SDA/SCL Capacitance	C <sub>I</sub>		-		10	pF
Pulse Width of Spike Suppressed by Input Filter	t <sub>sp</sub>		50			ns
High Period for SCL Clock	t <sub>HIGH</sub>	f <sub>SCL</sub> = 400 kHz	0.6			μS
Low Period for SCL Clock	t <sub>LOW</sub>	f <sub>SCL</sub> = 400 kHz	1.3			μS
Serial Data Set-up Time	t <sub>su:dat</sub>		100			ns
Serial Data Hold time	t <sub>HD:DAT</sub>		0			sec
Valid Data Time	t <sub>vd:dat</sub>	SCL Low to SDA Output Valid			0.9	μS
Valid Data Time for ACK	t <sub>VD:ACK</sub>	ACK from SCL Low to SDA Low			0.9	μS
I <sup>2</sup> C Bus Free Time Between Start and Stop	t <sub>BUF</sub>		1.3			μS
I <sup>2</sup> C Fall Time (Both SCL and SDA)	$t_{\scriptscriptstylefCL}$				300	ns
I <sup>2</sup> C Rise Time (Both SCL and SDA)	t <sub>rCL</sub>				300	ns
I <sup>2</sup> C Start or Repeated Start Condition Set-up Time	t <sub>su:sta</sub>		0.6			μS
I <sup>2</sup> C Start or Repeated Start Condition Hold Time	t <sub>hd:sta</sub>		0.6			μS

Parameter	Symbol	Conditions  SOURCE = 0 V $T_{J} = -40$ °C to 125 °C  (Unless Otherwise Specified)	Min	Тур	Max	Units
I <sup>2</sup> C Bus Specifications (S	DA and SCL P	ins) *See Note B				
I <sup>2</sup> C Stop Condition Setup Time	t <sub>su:sto</sub>		0.6			μS
Capacitive Load	C <sub>B</sub>				400	pF
Noise Margin at the Low Level	V <sub>NL</sub>		0.1 × uVCC			V
Noise Margin at the High Level	V <sub>NH</sub>		0.1 × uVCC			V
SCL Pin Interrupt Timer	t <sub>INT(SCL)</sub>	T <sub>1</sub> = 25 °C	50			μS

### Notes:

- A. This parameter is derived from characterization.
- B. This parameter is guaranteed by design.
- C. Use 1% tolerance resistor.
- D. To ensure correct current limit it is recommended that nominal 0.47  $\mu$ F / 4.7  $\mu$ F capacitors are used. In addition, the BPP capacitor value tolerance should be equal or better than indicated below across the ambient temperature range of the target application. The minimum and maximum capacitor values are quaranteed by characterization.

Nominal BPP Pin Capacitor Value	Tolerance Relative to Nominal Capacitor Value	
	Minimum	Maximum
<b>0.47</b> μF	-60%	+100%
4.7 μF	-50%	N/A

E. Settling delay in averaging register will increase total observed time under light and no-load conditions.

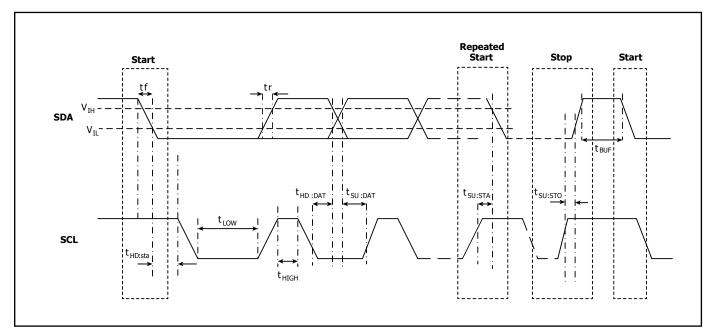


Figure 38. I<sup>2</sup>C Timing Diagram.

# **Performance Curves**

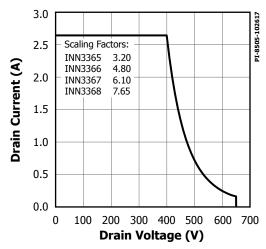


Figure 39. Maximum Allowable Drain Current vs. Drain Voltage.

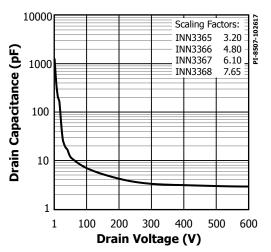


Figure 41. C<sub>oss</sub> vs. Drain Voltage.

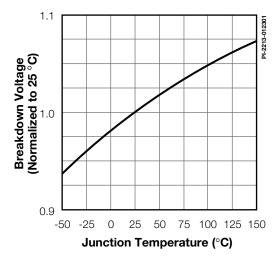


Figure 43. Breakdown vs. Temperature.

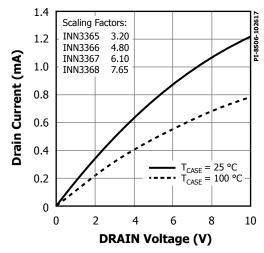


Figure 40. Output Characteristics.

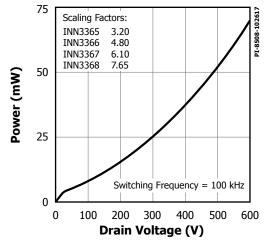


Figure 42. Drain Capacitance Power.

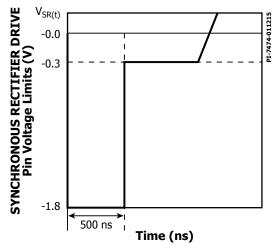


Figure 44. SYNCHRONOUS RECTIFIER DRIVE Pin Negative Voltage.

# **Performance Curves (cont.)**

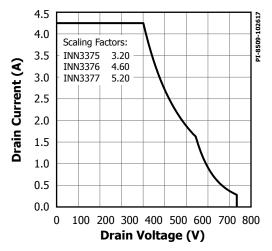


Figure 45. Maximum Allowable Drain Current vs. Drain Voltage.

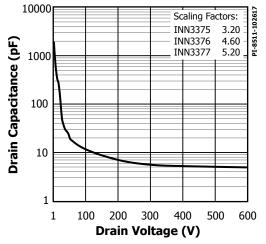


Figure 47. C<sub>oss</sub> vs. Drain Voltage.

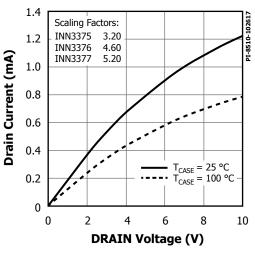


Figure 46. Output Characteristics.

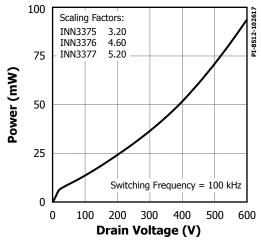


Figure 48. Drain Capacitance Power.

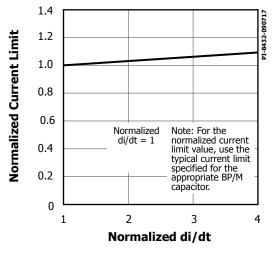
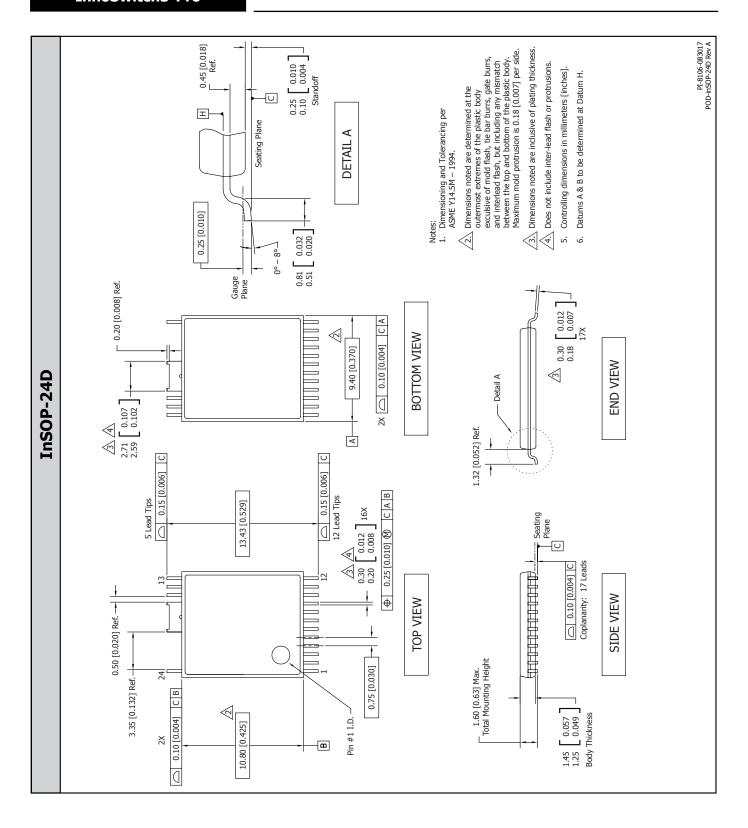


Figure 49. Standard Current Limit vs. di/dt.



# **Part Ordering Table**

Summary Features	H301
I <sub>LIM</sub> Selectable	Yes
Over-Temperature Protection	Hysteretic
Line OV/UV	Enabled
Line UV Timer (32 ms or 400 ms)	32 ms
IS Pin Short Fault Detection	Disabled

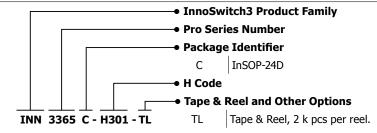
# **MSL Table**

Part Number	MSL Rating
INN33xxC	3

# **ESD and Latch-Up Table**

Test	Conditions	Results
Latch-up at 125 °C	JESD78D	$> \pm 100$ mA or $> 1.5 \times V_{MAX}$ on all pins
Charge Device Model ESD	ANSI/ESDA/JEDEC JS-002-2014	> ±500 V on all pins
Human Body Model ESD	ANSI/ESDA/JEDEC JS-002-2014	> ±2 kV on all pins

# **Part Ordering Information**





Revision	Notes	Date
С	Code L release.	03/18
D	Added READ13, 14, 15 telemetry registers. Updated H301 feature summary. Clarified register descriptions.	06/18
Е	Register fixes, schematic updates, added CTI parameter.	08/18

## For the latest updates, visit our website: www.power.com

Power Integrations reserves the right to make changes to its products at any time to improve reliability or manufacturability. Power Integrations does not assume any liability arising from the use of any device or circuit described herein. POWER INTEGRATIONS MAKES NO WARRANTY HEREIN AND SPECIFICALLY DISCLAIMS ALL WARRANTIES INCLUDING, WITHOUT LIMITATION, THE IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE, AND NON-INFRINGEMENT OF THIRD PARTY RIGHTS.

### **Patent Information**

The products and applications illustrated herein (including transformer construction and circuits external to the products) may be covered by one or more U.S. and foreign patents, or potentially by pending U.S. and foreign patent applications assigned to Power Integrations. A complete list of Power Integrations patents may be found at www.power.com. Power Integrations grants its customers a license under certain patent rights as set forth at www.power.com/ip.htm.

#### **Life Support Policy**

POWER INTEGRATIONS PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF THE PRESIDENT OF POWER INTEGRATIONS. As used herein:

- 1. A Life support device or system is one which, (i) is intended for surgical implant into the body, or (ii) supports or sustains life, and (iii) whose failure to perform, when properly used in accordance with instructions for use, can be reasonably expected to result in significant injury or death to the user.
- 2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

Power Integrations, the Power Integrations logo, CAPZero, ChiPhy, CHY, DPA-Switch, EcoSmart, E-Shield, eSIP, eSOP, HiperPLC, HiperPFS, HiperTFS, InnoSwitch, Innovation in Power Conversion, InSOP, LinkSwitch, LinkZero, LYTSwitch, SENZero, TinySwitch, TOPSwitch, PI, PI Expert, SCALE, SCALE-1, SCALE-2, SCALE-3 and SCALE-iDriver, are trademarks of Power Integrations, Inc. Other trademarks are property of their respective companies. ©2018, Power Integrations, Inc.

# **Power Integrations Worldwide Sales Support Locations**

## **World Headquarters**

5245 Hellyer Avenue San Jose, CA 95138, USA Main: +1-408-414-9200 Customer Service:

Worldwide: +1-65-635-64480 Americas: +1-408-414-9621 e-mail: usasales@power.com

## China (Shanghai)

Rm 2410, Charity Plaza, No. 88 North Caoxi Road Shanghai, PRC 200030 Phone: +86-21-6354-6323 e-mail: chinasales@power.com

## China (Shenzhen)

17/F, Hivac Building, No. 2, Keji Nan Bangalore-560052 India 8th Road, Nanshan District, Shenzhen, China, 518057 Phone: +86-755-8672-8689 e-mail: chinasales@power.com

**Germany** (AC-DC/LED Sales) Lindwurmstrasse 114

D-80337 München

Germany

Phone: +49-89-5527-39100 e-mail: eurosales@power.com

**Germany** (Gate Driver Sales)

HellwegForum 1 59469 Ense Germany

Tel: +49-2938-64-39990

e-mail: igbt-driver.sales@power.com e-mail: japansales@power.com

### India

#1, 14th Main Road Vasanthanagar Phone: +91-80-4113-8020 e-mail: indiasales@power.com

## Italy

Via Milanese 20, 3rd. Fl. 20099 Sesto San Giovanni (MI) Italy Phone: +39-024-550-8701 e-mail: eurosales@power.com

Yusen Shin-Yokohama 1-chome Bldg. Taiwan 1-7-9, Shin-Yokohama, Kohoku-ku Yokohama-shi, Kanagawa 222-0033 Japan Phone: +81-45-471-1021

# Korea

RM 602, 6FL Korea City Air Terminal B/D, 159-6 Samsung-Dong, Kangnam-Gu, Seoul, 135-728, Korea Phone: +82-2-2016-6610

e-mail: koreasales@power.com

## **Singapore**

51 Newton Road #19-01/05 Goldhill Plaza Singapore, 308900 Phone: +65-6358-2160

e-mail: singaporesales@power.com

5F, No. 318, Nei Hu Rd., Sec. 1

Nei Hu Dist.

Taipei 11493, Taiwan R.O.C. Phone: +886-2-2659-4570 e-mail: taiwansales@power.com

Building 5, Suite 21 The Westbrook Centre Milton Road Cambridge

CB4 1YG

Phone: +44 (0) 7823-557484 e-mail: eurosales@power.com